

Spintronics and Superconducting Spintronics based on Chiral Molecules

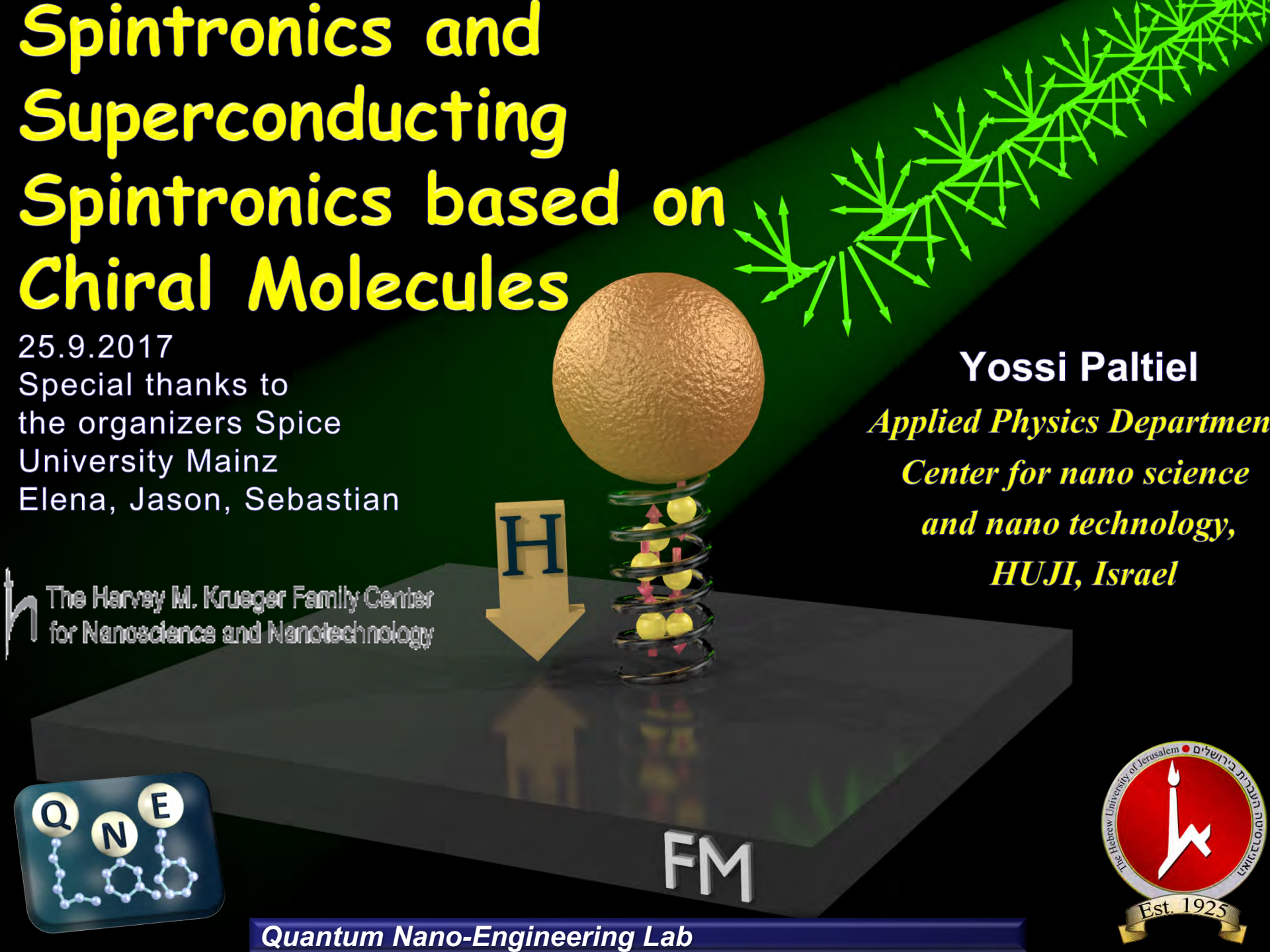
25.9.2017

Special thanks to
the organizers Spice
University Mainz
Elena, Jason, Sebastian

The Harvey M. Krueger Family Center
for Nanoscience and Nanotechnology

Yossi Paltiel

*Applied Physics Department
Center for nano science
and nano technology,
HUJI, Israel*



Quantum Nano-Engineering Lab

Jerusalem and The Hebrew University



Inauguration ceremony 1925



The Hebrew University of Jerusalem is Israel's oldest (1925) university. The First Board of Governors included **Albert Einstein, Sigmund Freud, Martin Buber, and Chaim Weizmann.**

In the Academic Ranking of World Universities index, **Hebrew University is the top university in Israel and among the world's 100 top universities. (ranked 57)**

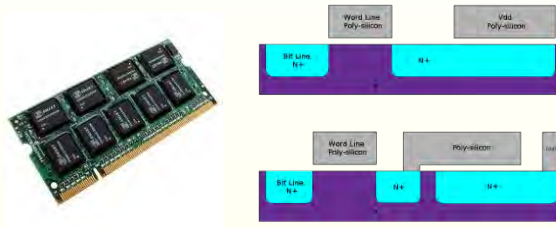
Memory devices

Fast but need constant power

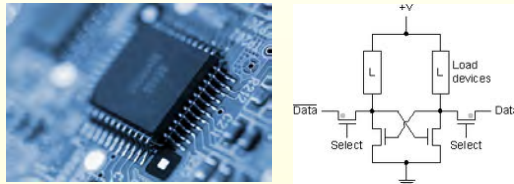
Slow last for 10 years

DRAM - Dynamic random-access memory

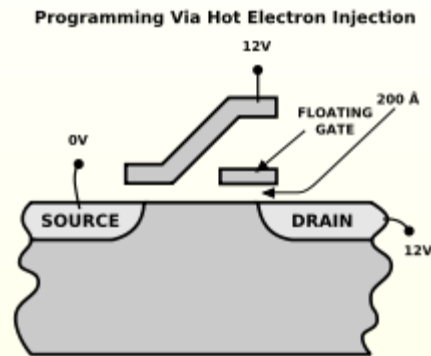
refreshed periodically



SRAM - Static random-access memory
Does not need to be periodically refreshed



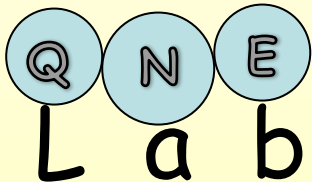
Flesh memory



All existing memory technologies challenged when critical size is smaller than 45 nm

We are looking for:

No need for power, long lived, fast, standard technology

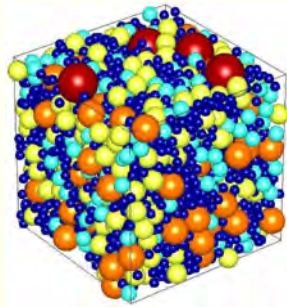


Simple Universal Magnetic Memory

Fast



Dense



**Non-
Volatile**



**Power
efficient**



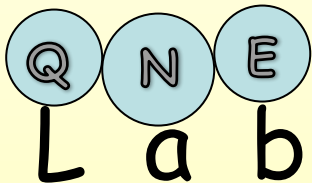
**The industry needs are met without compromising in
cost, compatibility to standard Si process
& complexity of design**

Spin Electronics

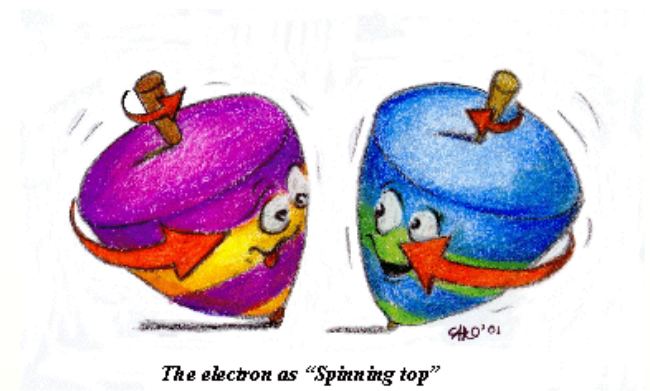
Electrons have charge and spin 1/2



- Conventional electronic devices ignore the spin property and rely strictly on the transport of the electrical charge of electrons
- Adding the spin degree of freedom provides new effects, new capabilities and new functionalities

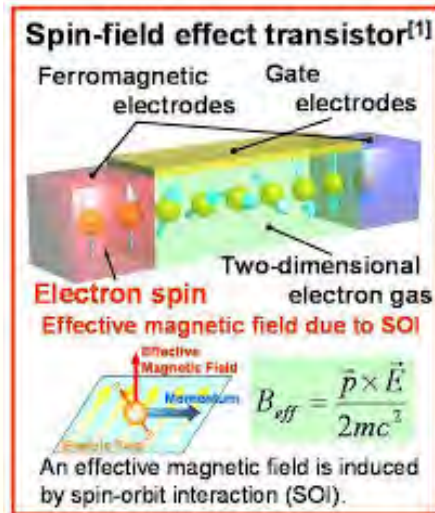
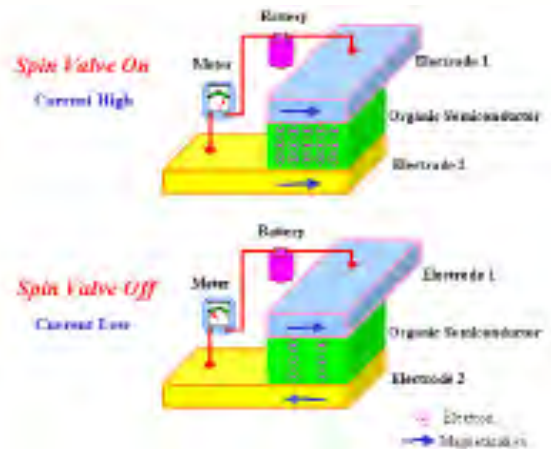


Why Spintronics?

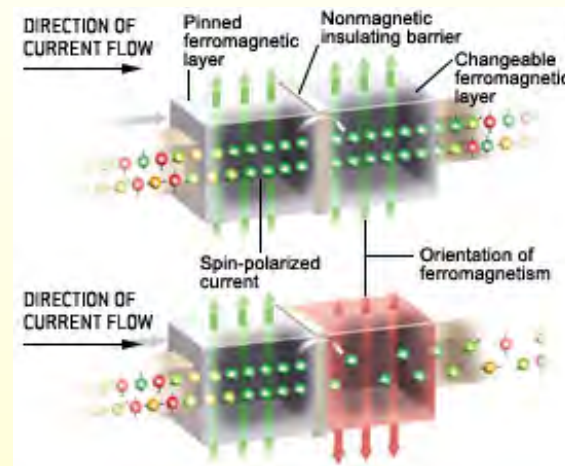
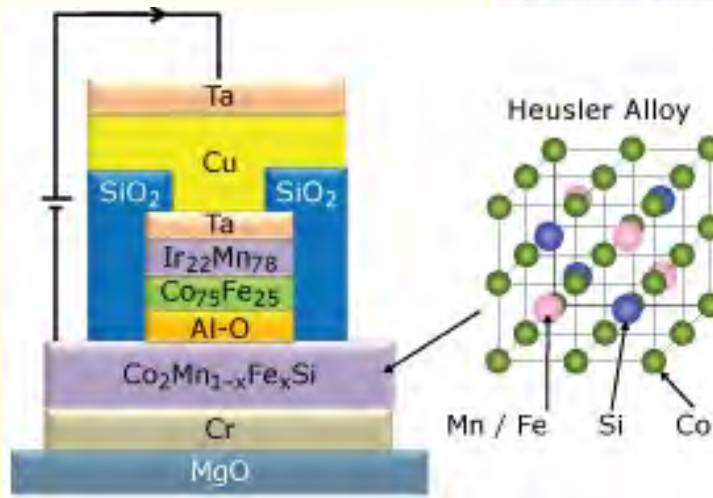


- **Energy and heat-** For Spintronics, less energy
- **Quantum effects** -It may be a way for introducing the spin properties to our tool arsenal.

Spintronics Devices

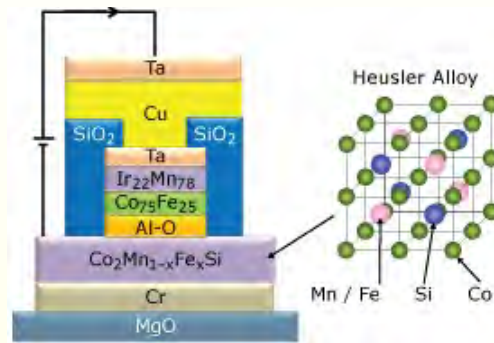


The 2007 Nobel Prize in Physics was awarded to : [Albert Fert](#) and [Peter Grünberg](#) for the discovery of GMR



Two Major Problems

- **Material problem**

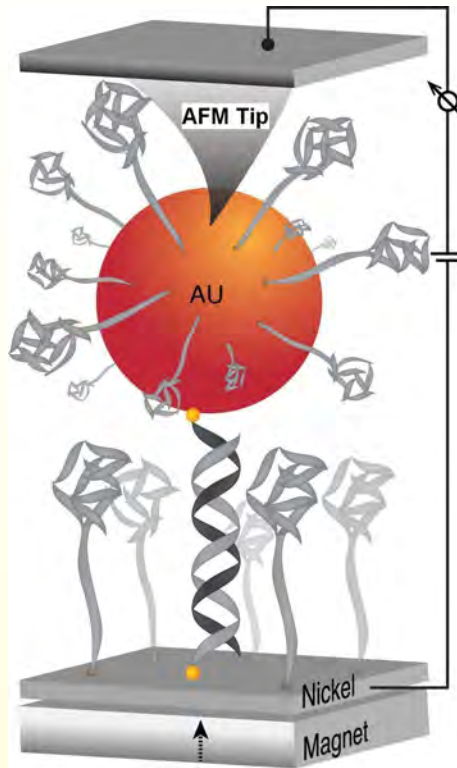


- **Spin separation requires high current**

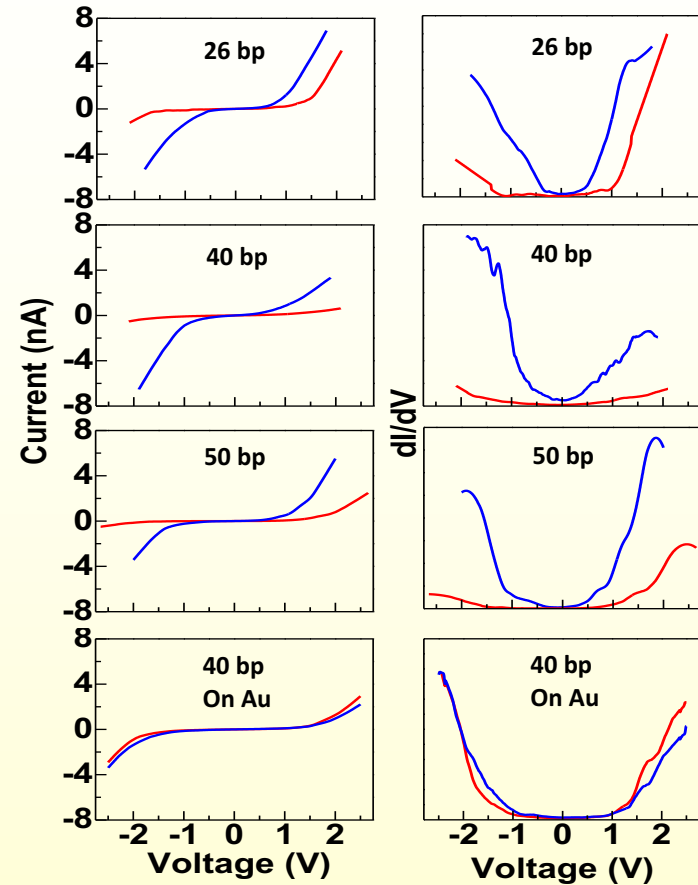


The CISS Effect

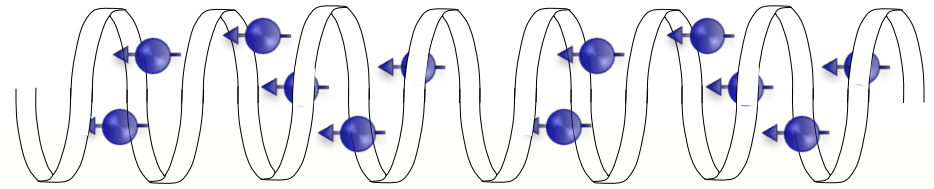
Chiral Induced Spin Selectivity - CISS



Zuoti Xie, Tal Markus, Sidney Cohen, Zeev Vager,
Rafael Gutierrez, Ron Naaman
Nano Letters, **11**, 4652–4655 (2011).



Theory



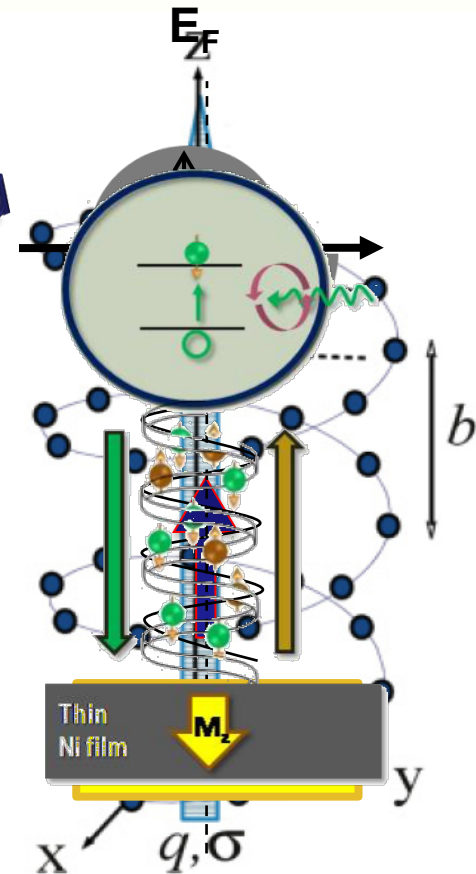
- Chirality Induced Spin-selectivity (CISS) effect

Major Transport mechanism •
is Spin-Orbit Coupling (SOC)

$$\vec{B} = \frac{\vec{v}}{c^2} \times \vec{L}$$



Rashba like term due to chiral orbit

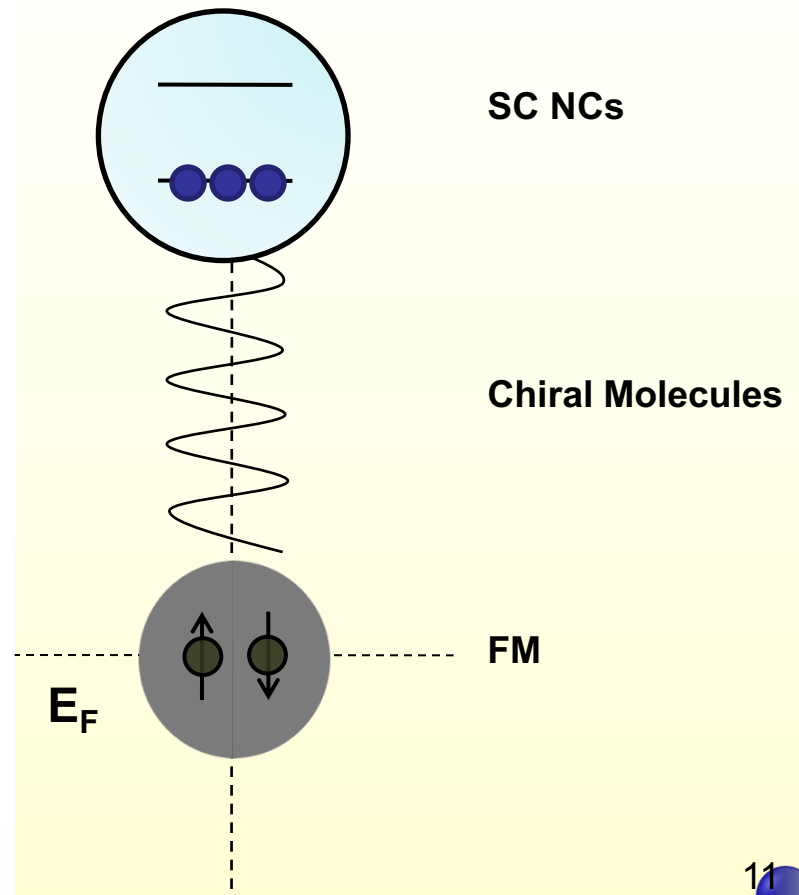


Q N E
L a b

Gutierrez, E. D'iaz, R. Naaman, and G. Cuniberti¹, PHYSICAL REVIEW B 85, 081404 (2012)

Transport Vs Optics

Chirality Induced Spin-selectivity (CISS) effect •

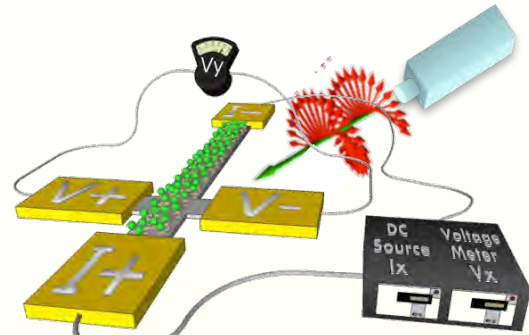


CISS Devices solves material problem

RT simple devices

Nano letters **14** 6042 (2014).

ACS Photonics, , **2** (10), pp 1476–1481 (2015).



Optical – photon driven:

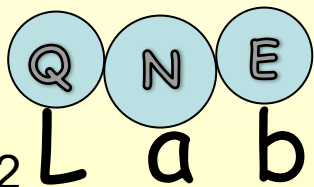
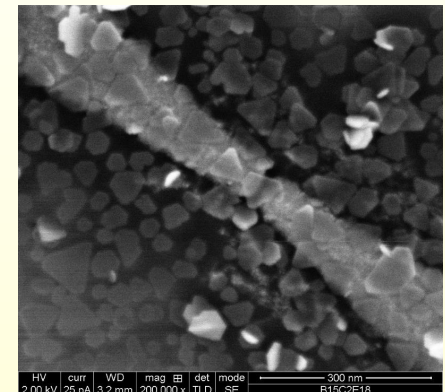
- Local magnetization/local optical memory.
- Nano metric charge separation.

Electrical – electrons driven:

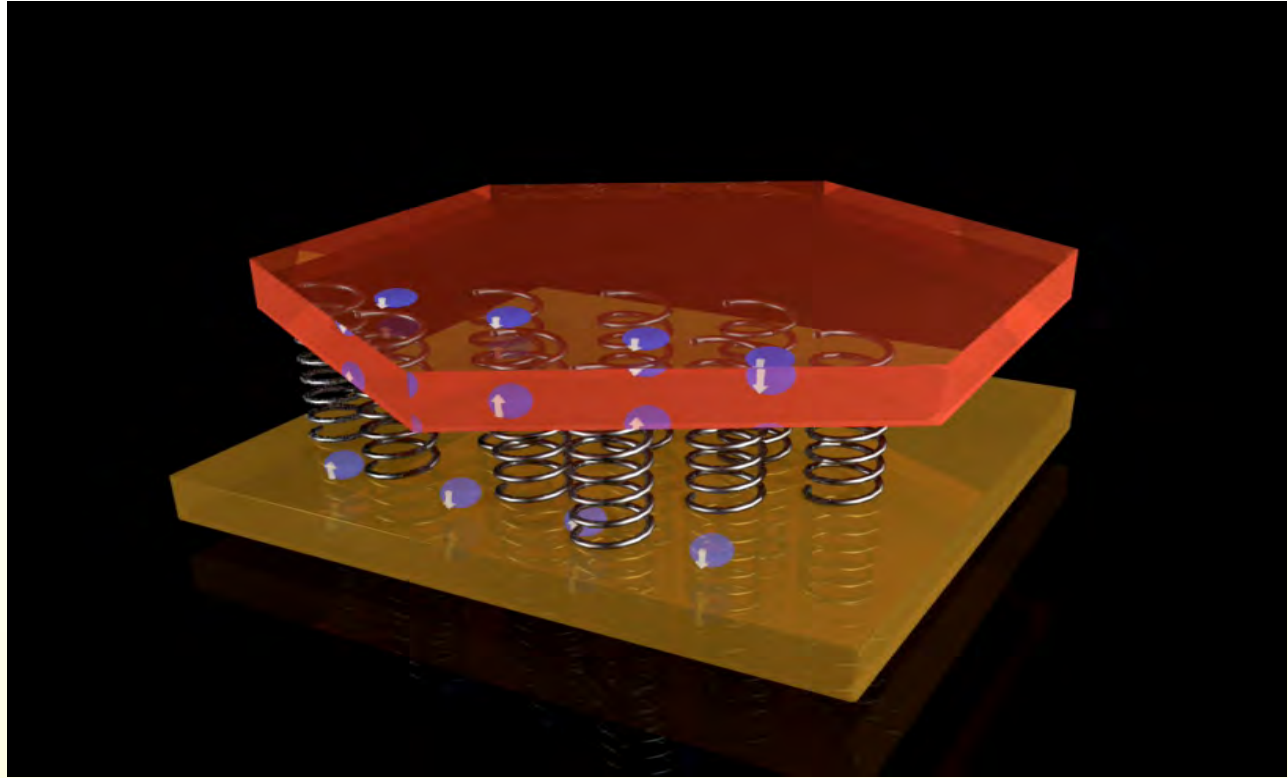
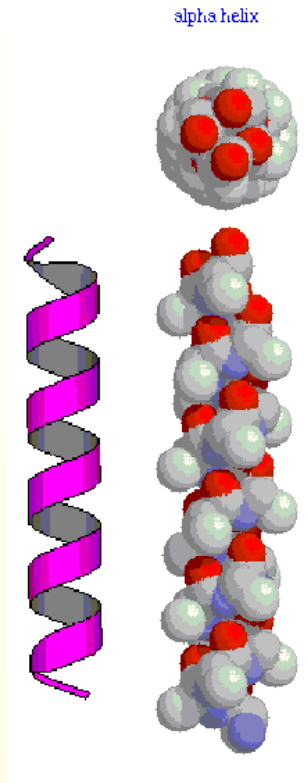
- Spin injector
- Nano memristor.

Nature Communications **4**, 2256 (2013).

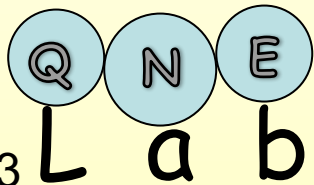
Applied Physics Letters, **105** 242408 (2015).



Electrical CISS Memory

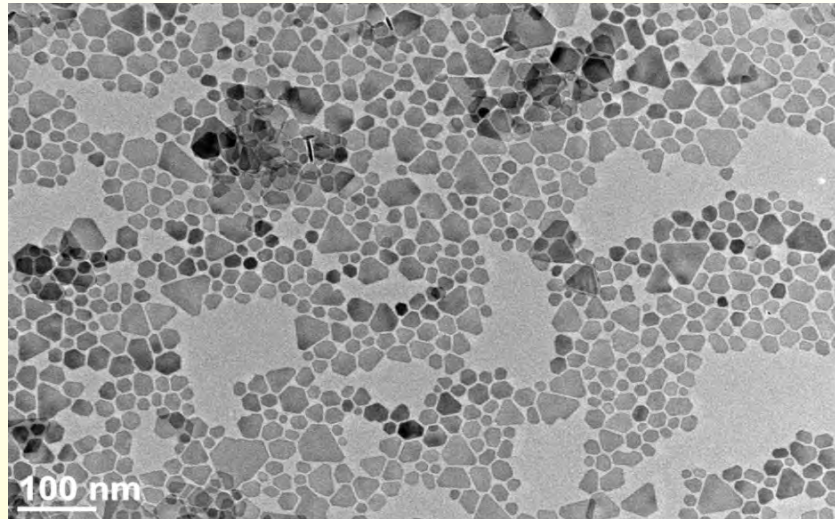


L or D PAL (polyalanine), thiolated α -helix -
CAAAAKAAAAKAAAAKAAAAKAAAAKAAAAK-SH
C, A, and K represent cysteine, alanine, and lysine



Room Temperatures CISS Memristors

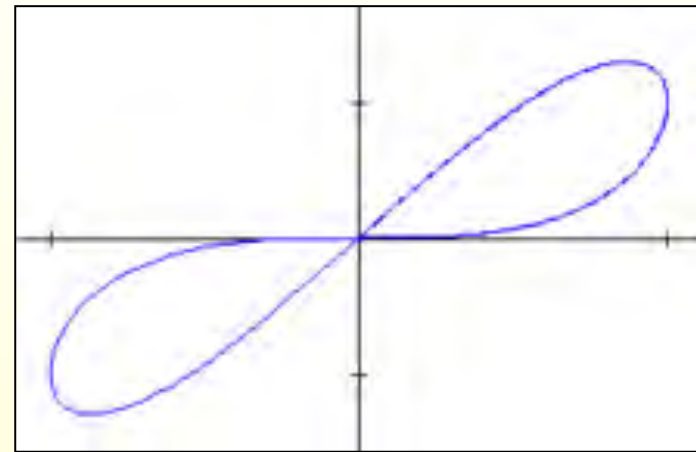
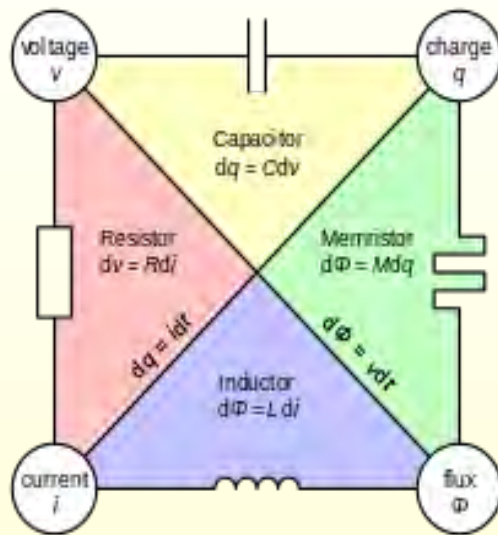
*Embedded memory using the
CISS effect and magnetic nano
particles*



FerroMagnetic Nano Platelets (FMNPs)

Two designs for embedded memory devices based on the CISS effect and magnetic nano palettes.

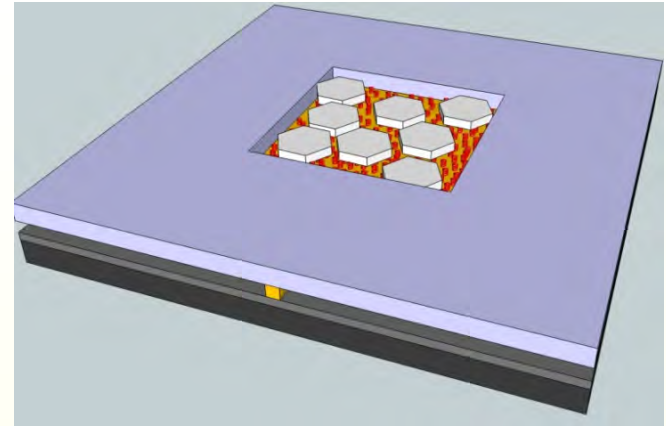
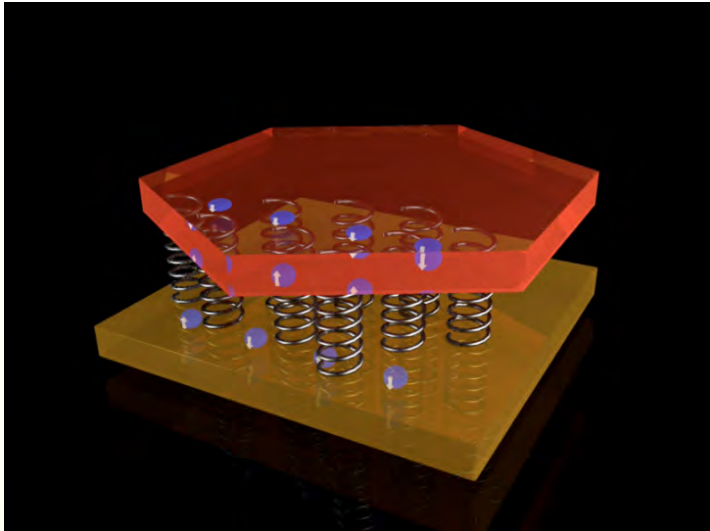
- Four layers vertical printable device (easy to fabricate).
- Lateral 40nm device based on two layers.



Different resistance states

Chua, L. O. (1971), "Memristor—The Missing Circuit Element", *IEEE Transactions on Circuit Theory*, CT-18 (5): 507-519

Vertical Memristor Device

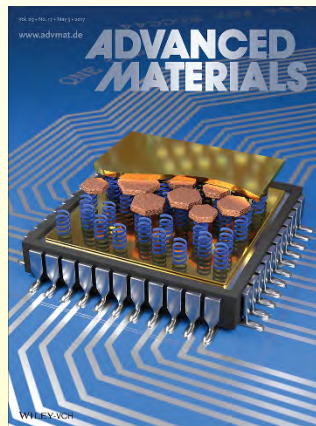


Bottom electrode •

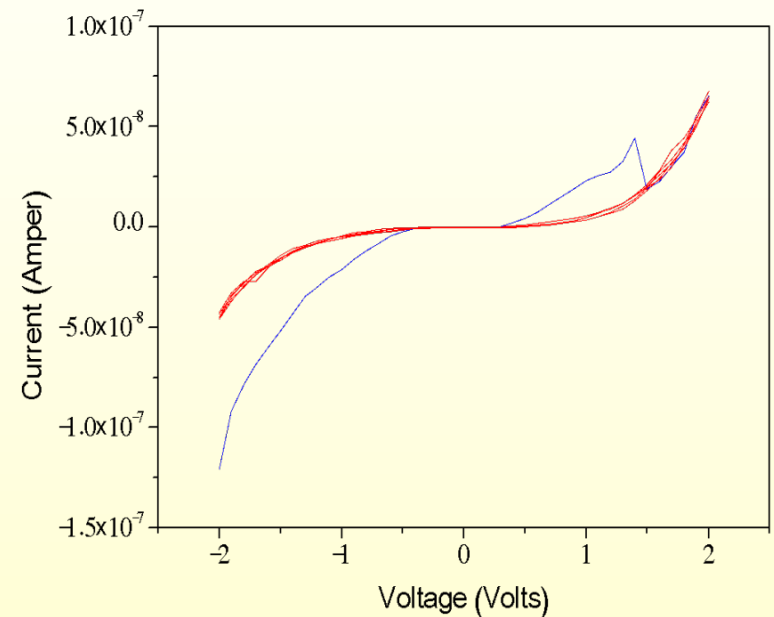
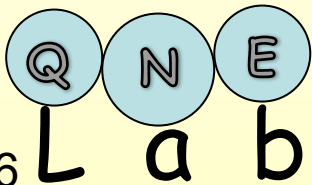
Adsorb AHPA-L or AHPA-D and multiple FMNPs •

Al_2O_3 tunnel barrier •

Top electrode •

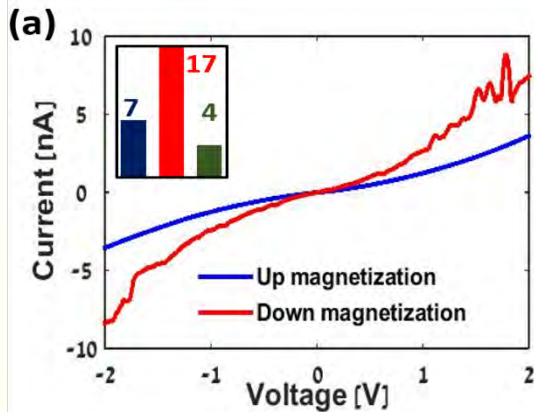


AHPA chiral molecules-
[H]-CAAAAKAAAAKAAAAKAAAAKAAAAK
AAAAKAAAAK-[OH]

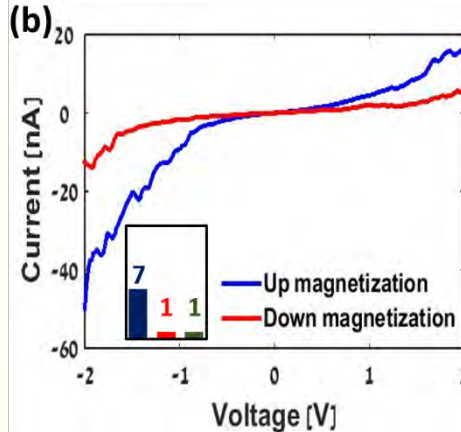


Vertical Memristor Device

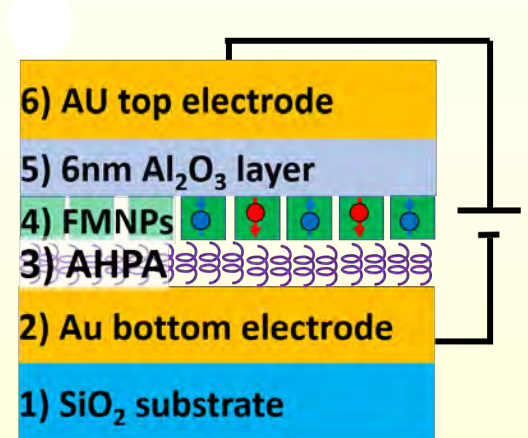
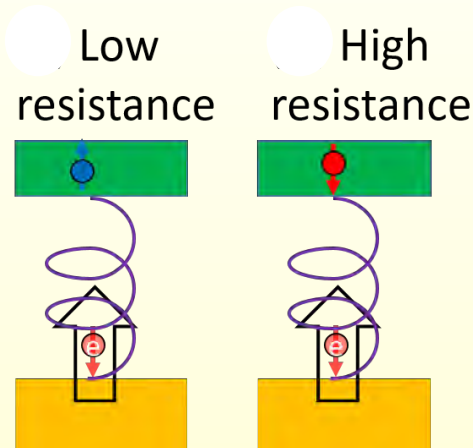
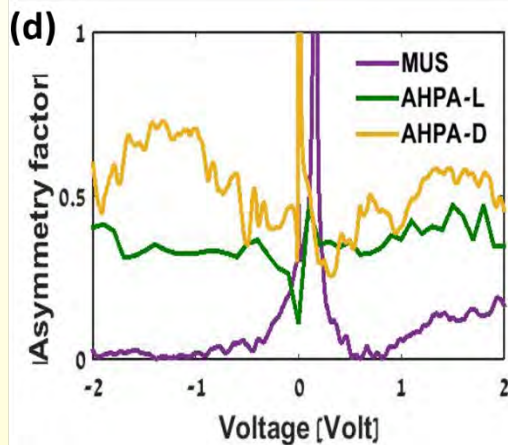
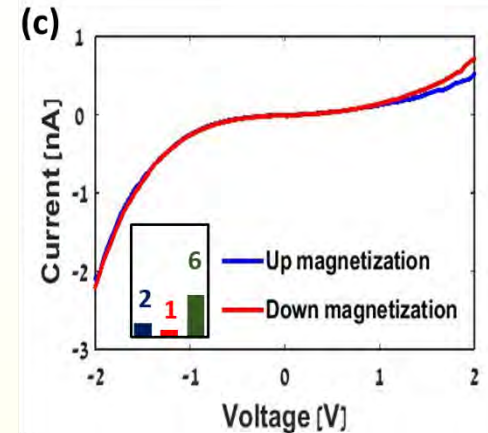
AHPA-L (α -Helix Poly-Alanine –L)



AHPA-D (α -Helix Poly-Alanine – D)



MUS- non-chiral 11-mercaptopundecyl-trimethoxysilane



Advance materials 2017

Quantum Nano Engineering Lab

1/21/20

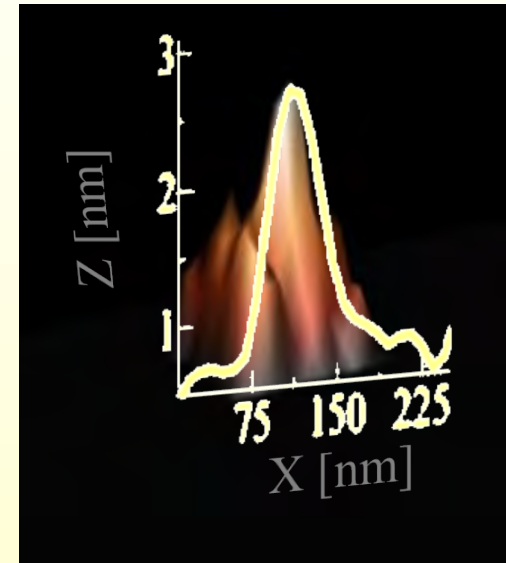
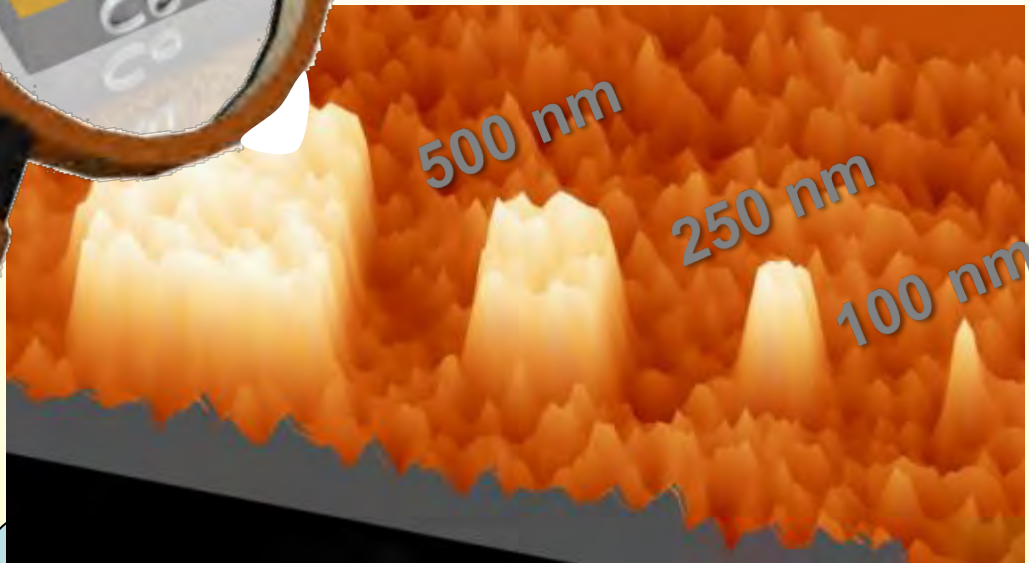
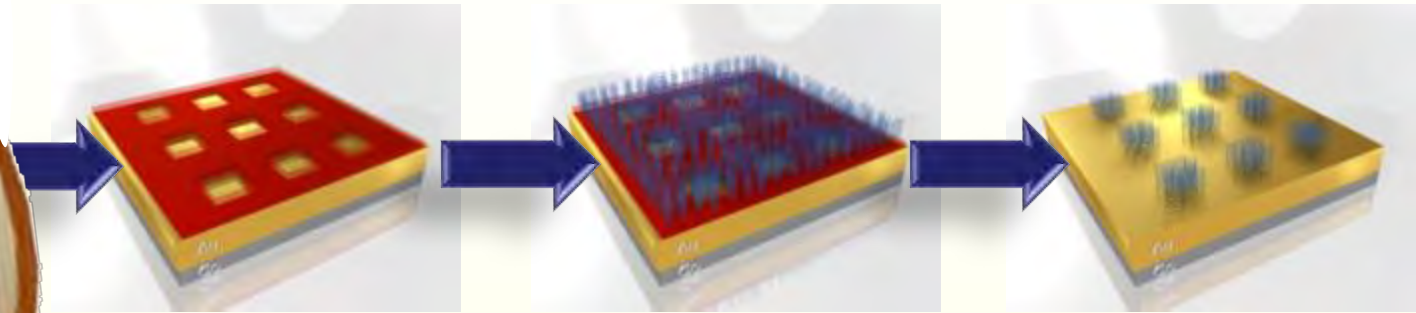
What can we say
about the
coherence in
CISS?

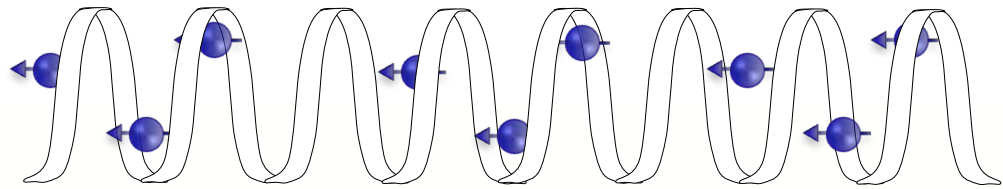
What happens
in equilibrium?



Magnetization with no current

Selective adsorption down to 50nm •

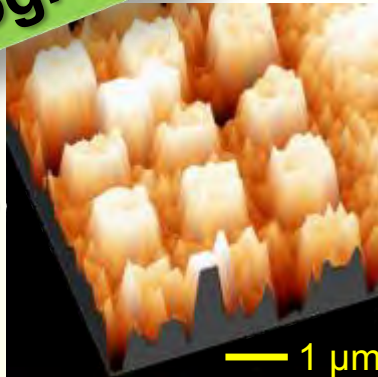




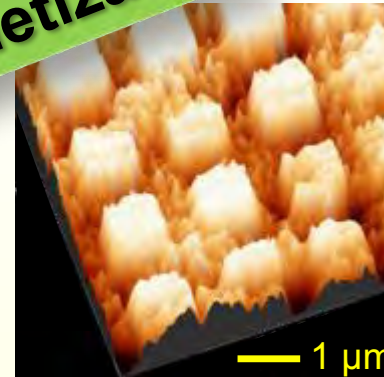
Selective adsorption -> Selective magnetization •

Topography

AHPA-L

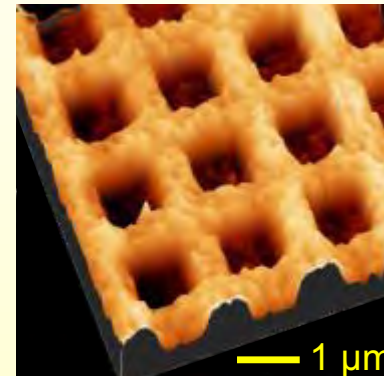
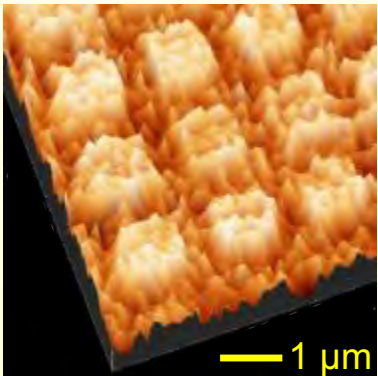


Magnetization

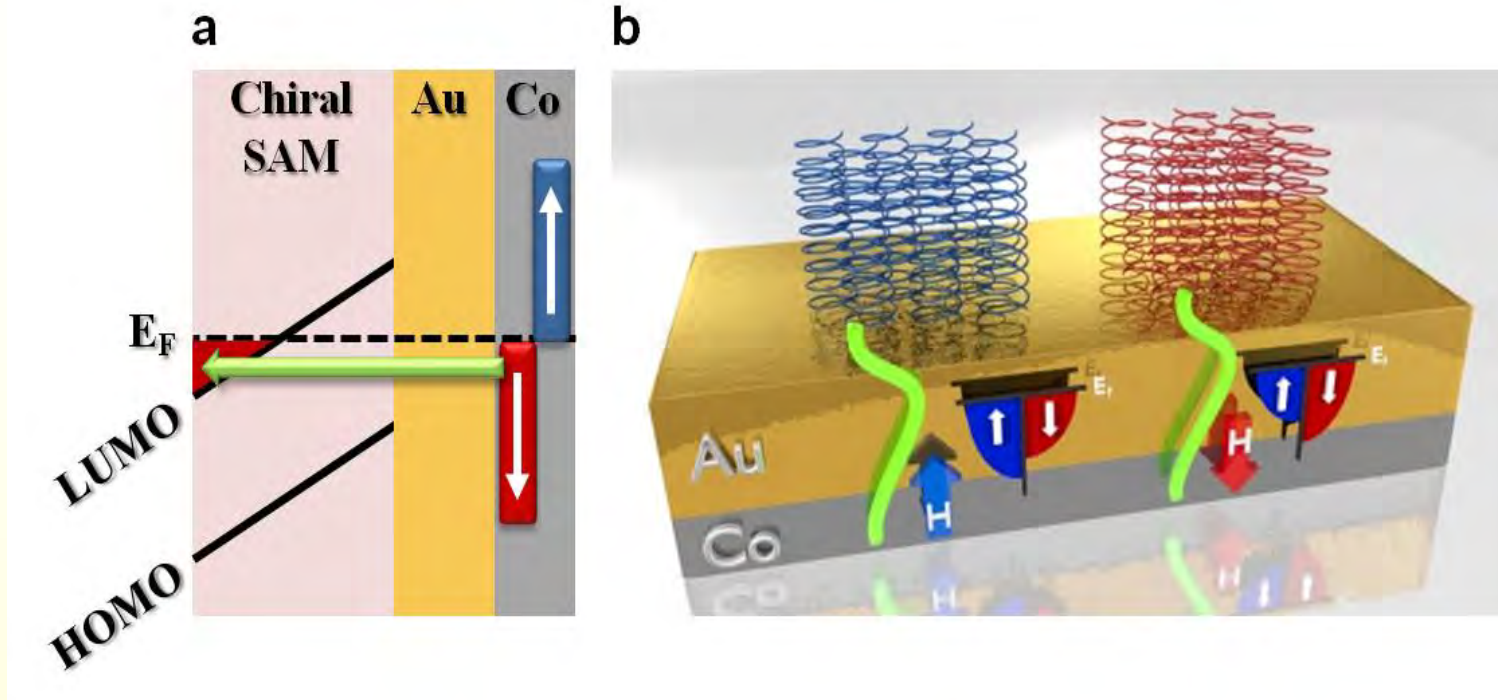


Ben Dor *et al.*
Nature
Communications
8 14567 (2017).

AHPA-D



Semi- Classical Vs Quantum



Fraction of a charge??

Coherent???

Magnetization with no current!!!!

Magnetization with no current?

- The current density required for the spin-transfer torque (STT) is of the order of 10^6 A/cm^2
- STT – current density equals $10^{25} \text{ electrons/s cm}^2$
- Adsorption of molecules $10^{13} \text{ molecules/cm}^2$



Here if 1 electron is transfer per
molecule
 $10^{13} \text{ molecules/cm}^2$

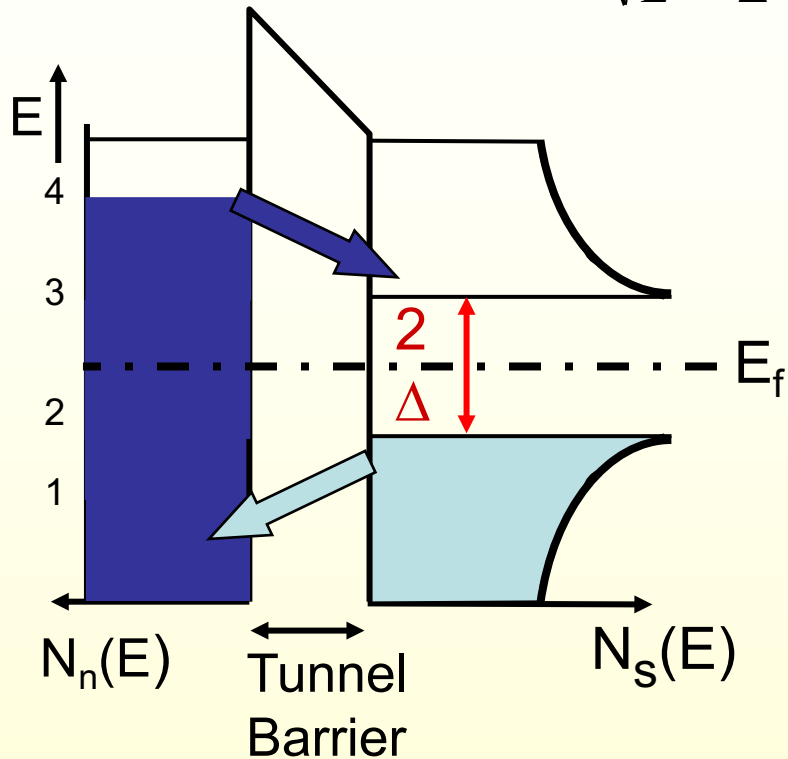
Do we have a spin induced long
range coherent order?
Or the CISS is creating a
local magnetic impurity?

superconducting
proximity effect?

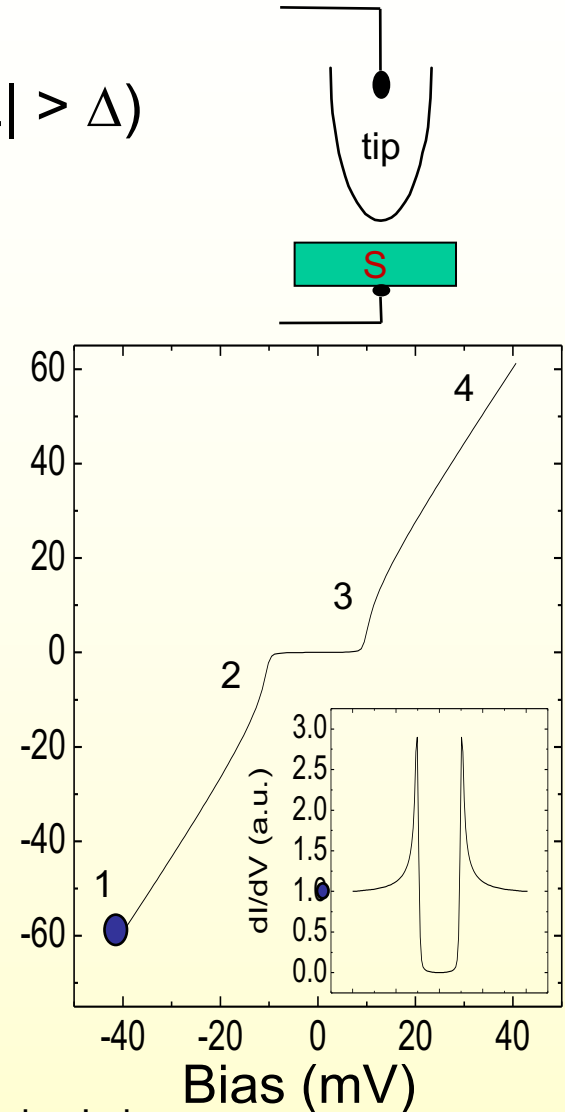


I-V & dI/dV-V Tunneling Spectroscopy

$$dI/dV \propto D_s(r, E) \propto \frac{|E|}{\sqrt{E^2 - \Delta^2}} \quad (|E| > \Delta)$$

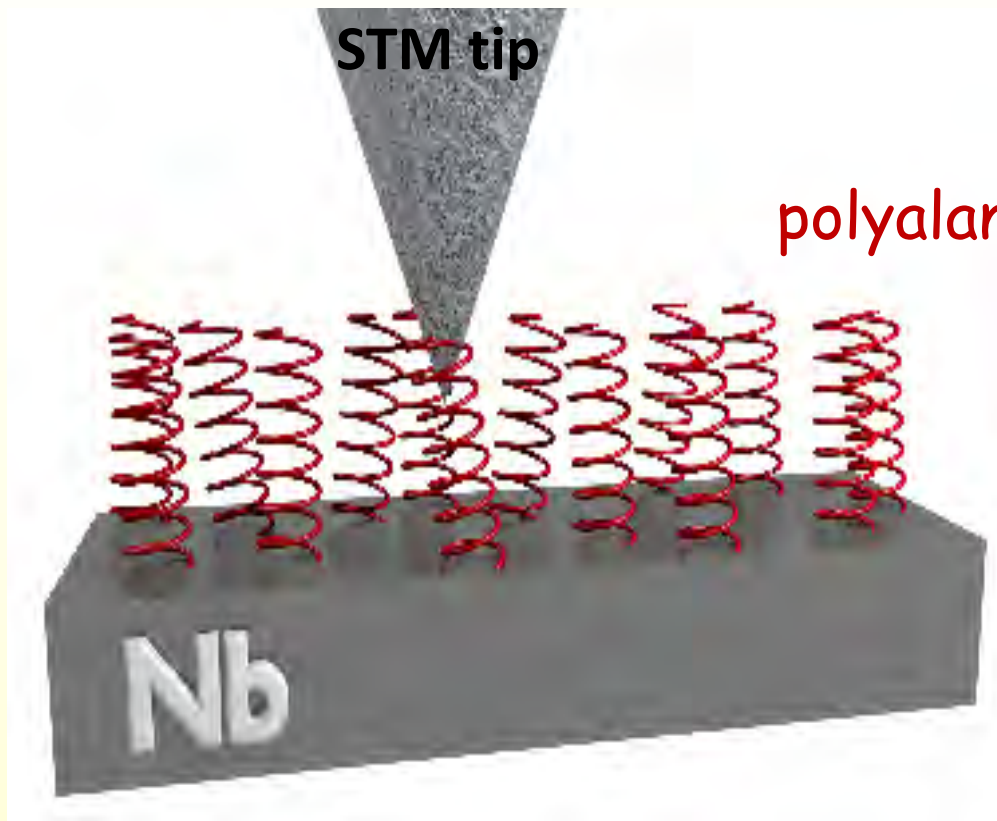


I (nA)



Measuring Scheme

So what will happen if we adsorb chiral molecules on superconductors surface?



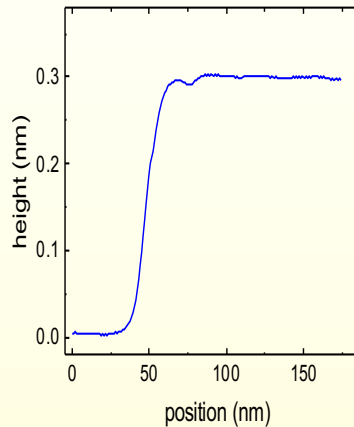
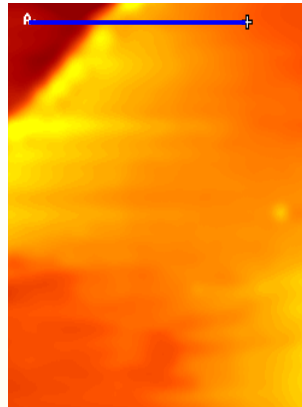
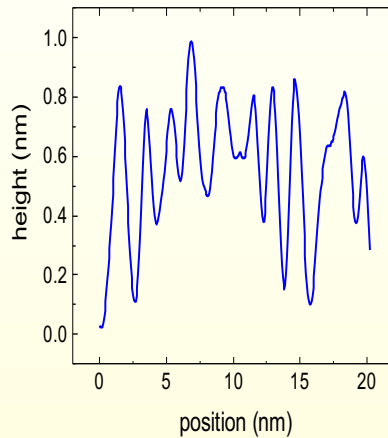
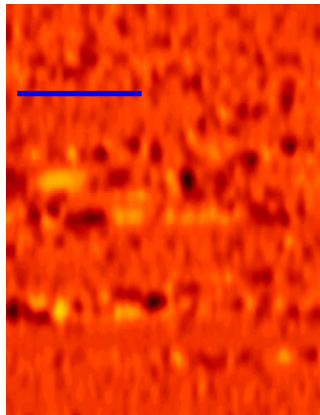
polyalanine alpha-helix

In collaboration with
Oded Millo

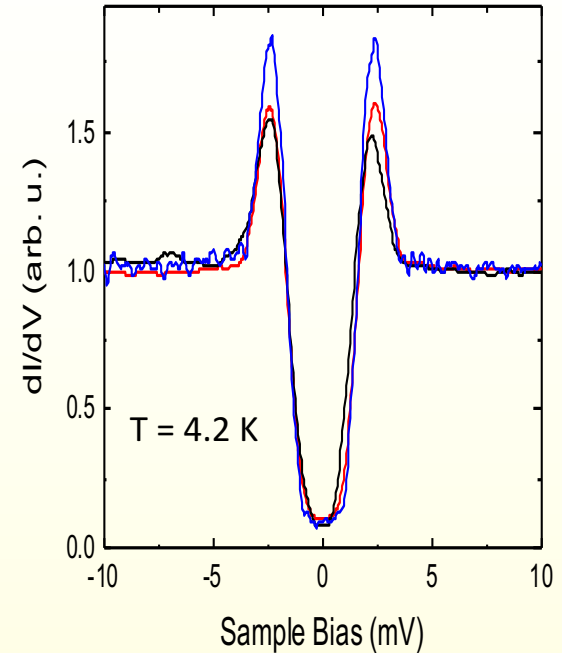
sample characterization

molecule-covered area

molecule-free area

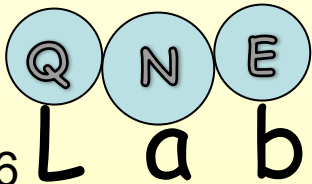


on pristine film
gaps of $\Delta \approx 1.55$ meV.

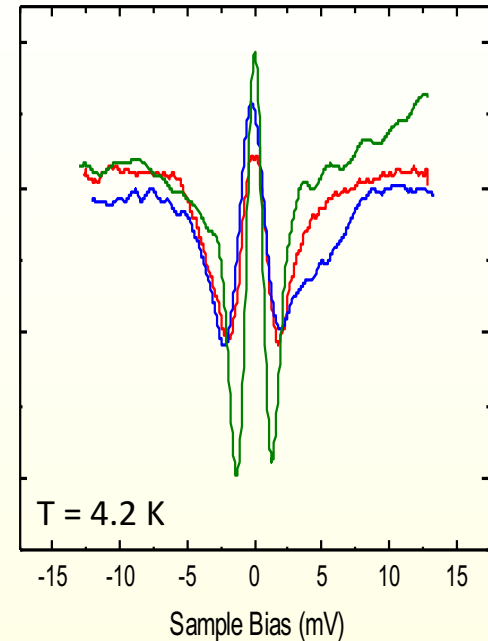
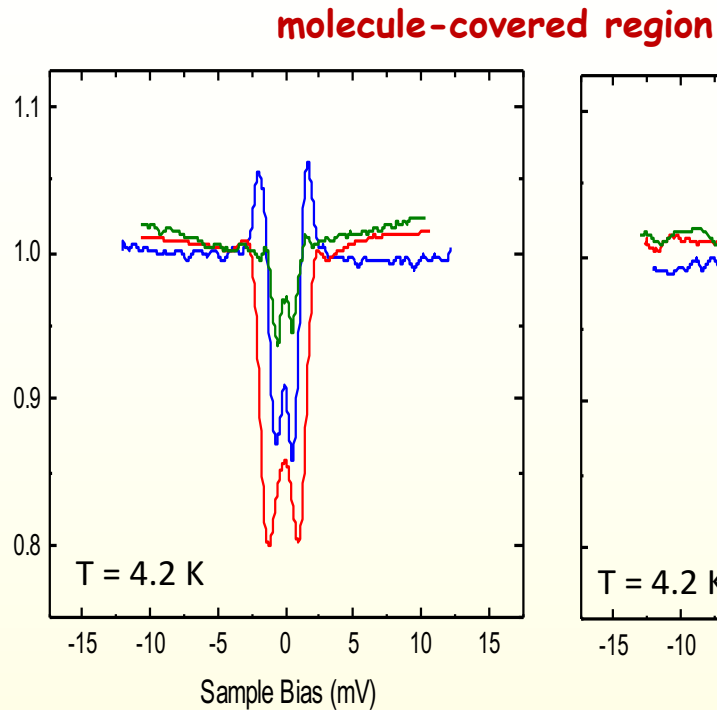
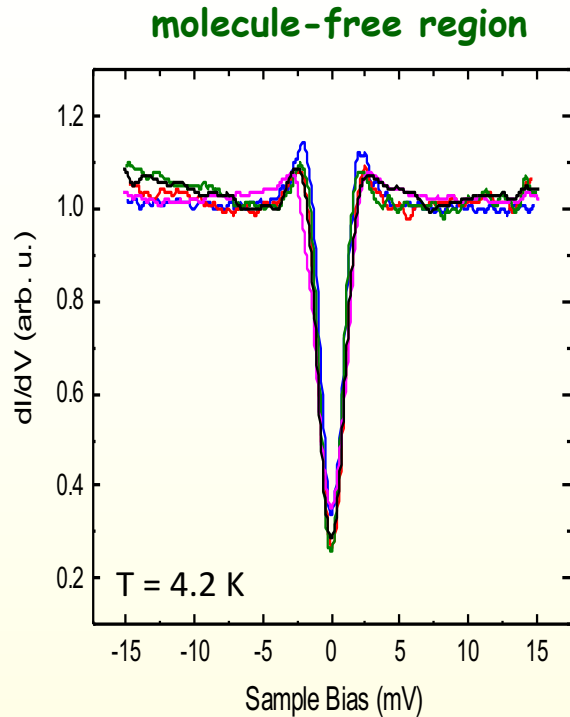


60 nm thick Nb films on Si. T_c between 7.5 to 8.5 K.

Polyalanine alpha-helix molecules, (~ 3 nm long, ~ 1 nm wide).



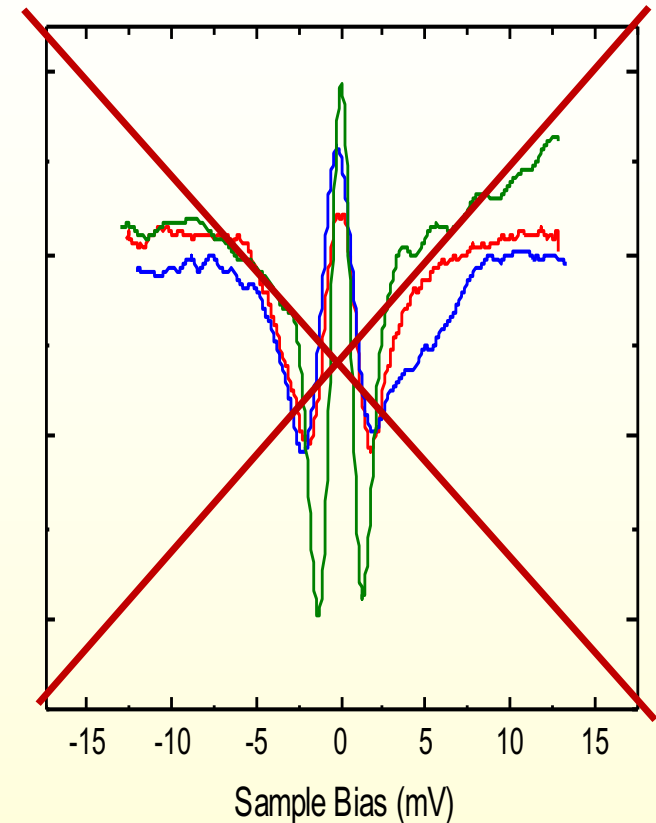
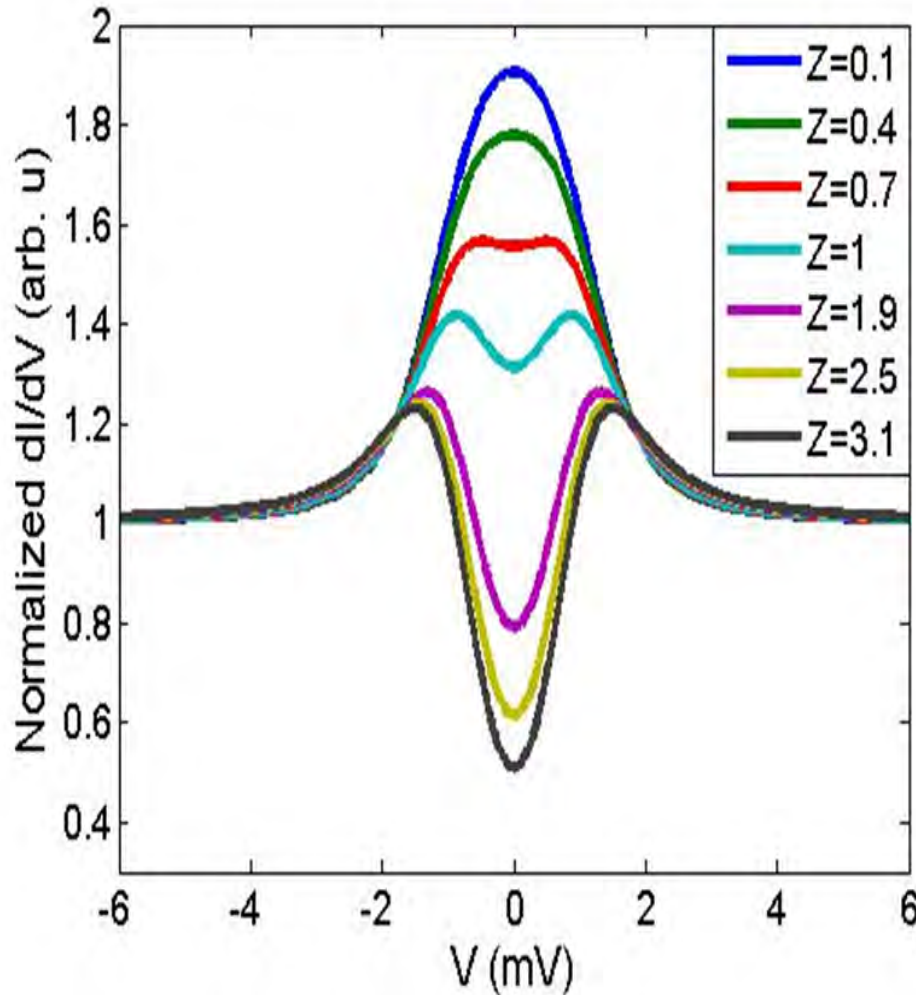
Three types of spectra



- **molecule-free regions:** smeared BCS-like spectra.
- **molecule covered regions:** zero-bias conductance peaks inside gaps.

Could s-wave symmetry explain these results?

BTK model for various barrier strength Z values

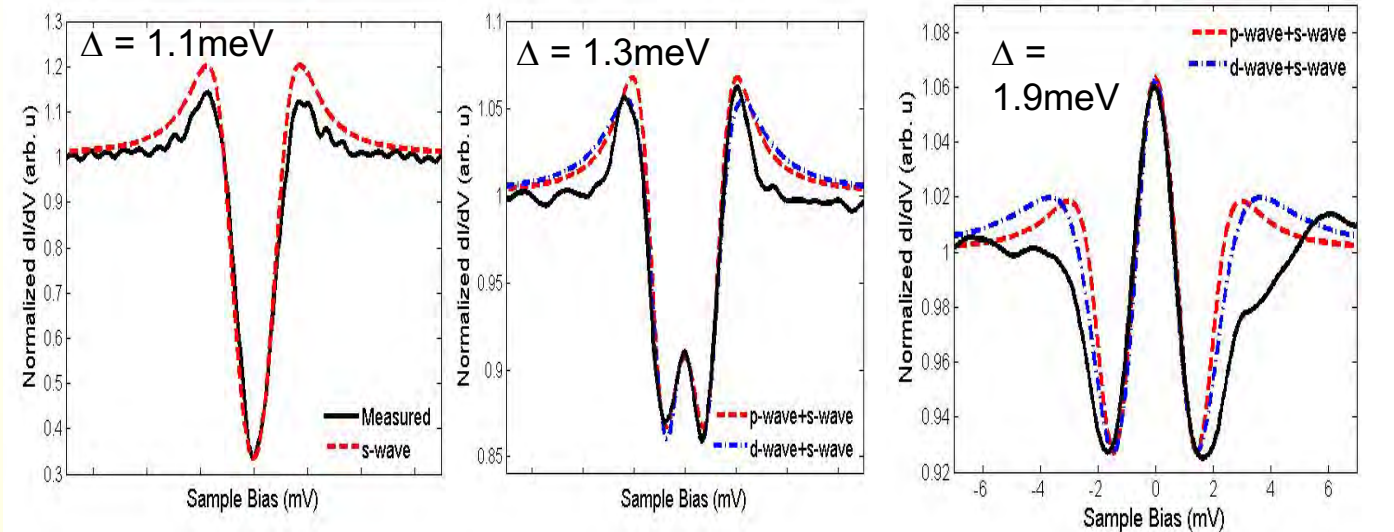


Fits to the three types of spectra

Combination of s-wave, d-wave and chiral p-wave pairing potentials. $T = 4.2$ K

chiral p-wave : $\Delta_{\uparrow\uparrow} = \Delta_0 \sin \theta (\cos \phi + i \sin \phi)$ (triplet)

d-wave ($d_{x^2-y^2}$) : $\Delta = \Delta_0 \cos(2\theta)$ (singlet or odd-frequency triplet)



s-wave only

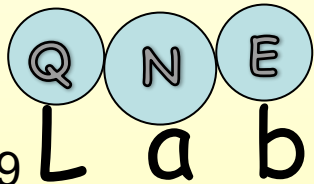
**p-wave + s-wave
(61% p-wave)**

**d-wave + s-wave
(50% p-wave)**

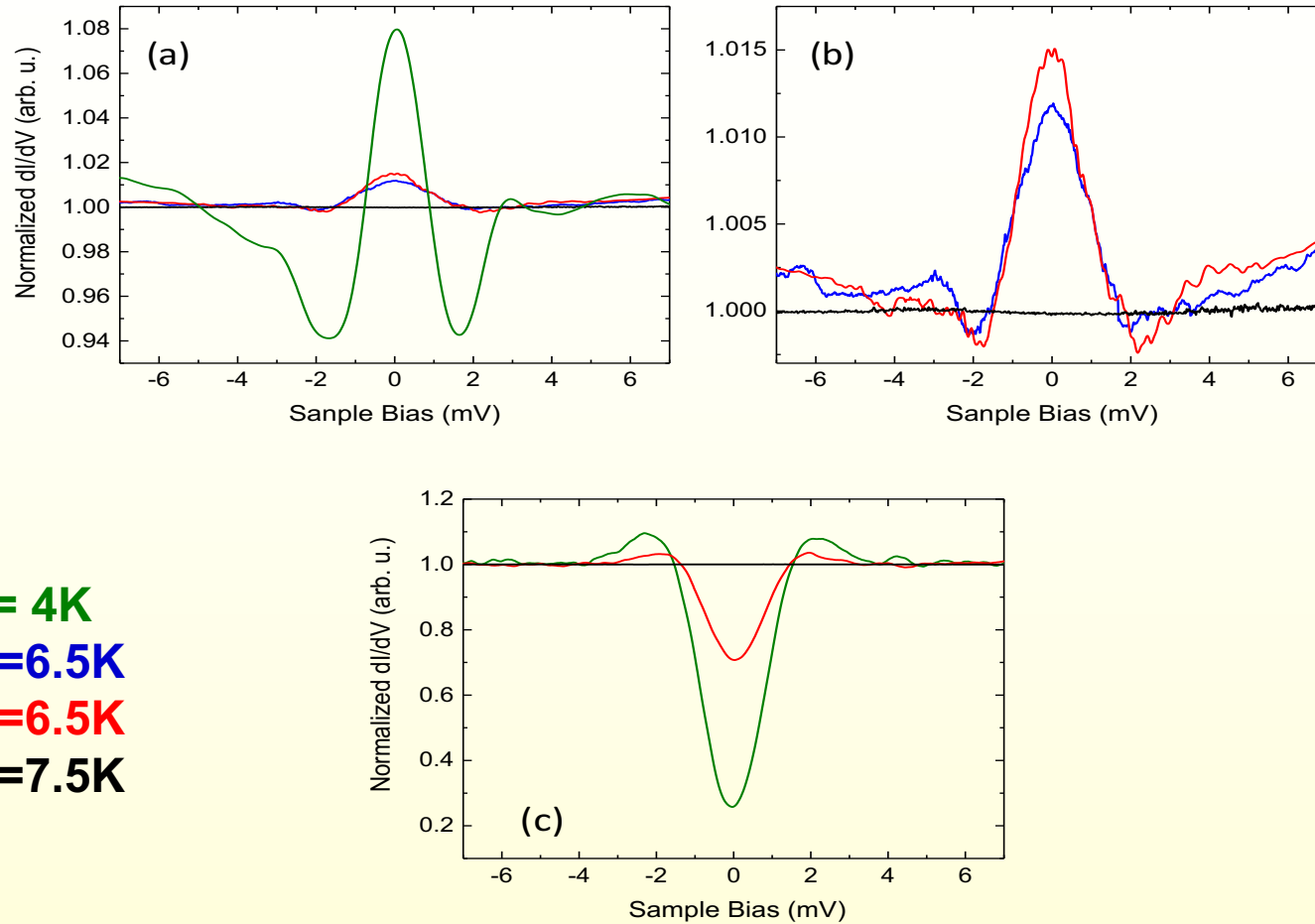
**p-wave + s-wave
(73% p-wave)**

**d-wave + s-wave
(65% p-wave)**

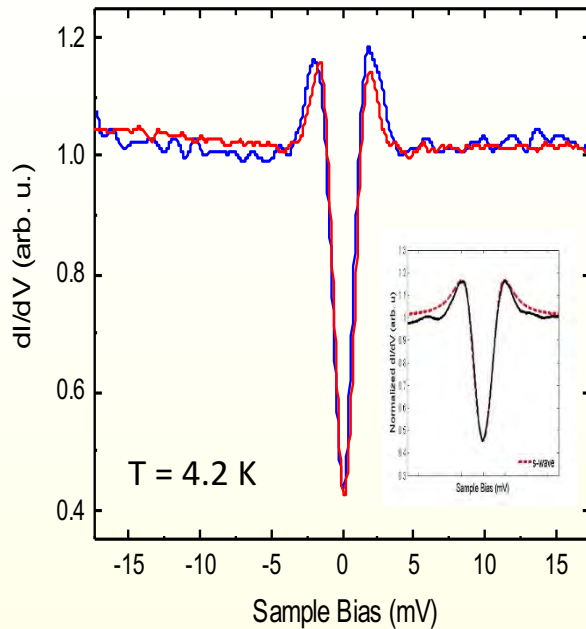
New J. Phys. 18 113048 (2016).



Temperature Dependence

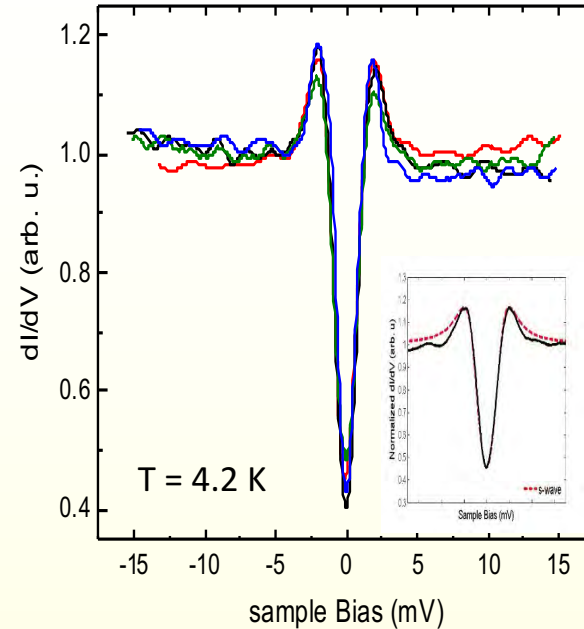


Control samples



all surface treatments
including solvent deposition,
but no molecules

$$T_C = 7.5 \text{ K}; \Delta \approx 1.1 \text{ meV}$$



non-chiral di-silane
molecules

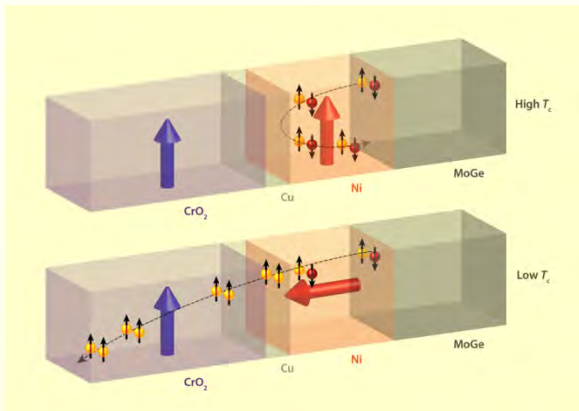
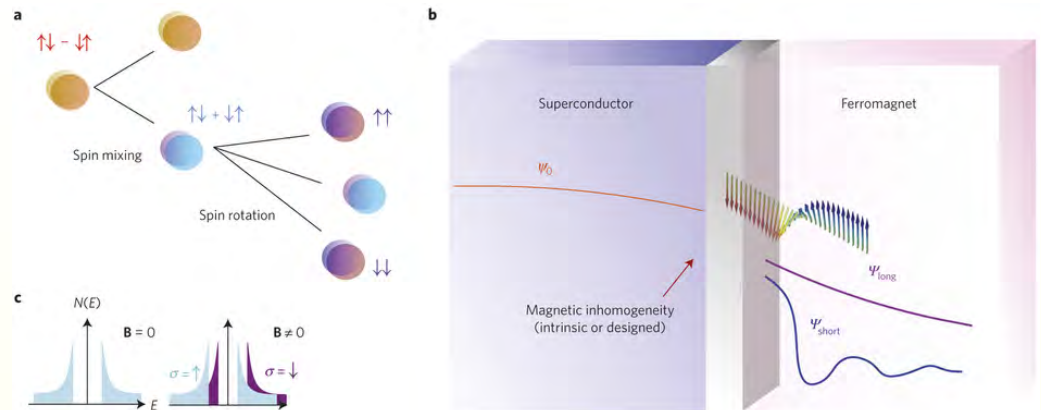
$$T_C = 8 \text{ K}; \Delta \approx 1.2 \text{ meV}$$

Superconducting Spintronics

Interaction between superconducting and spin-polarized orders

Superconducting spintronics

Jacob Linder & Jason W. A. Robinson
Nature Physics **11**, 307 (2015).

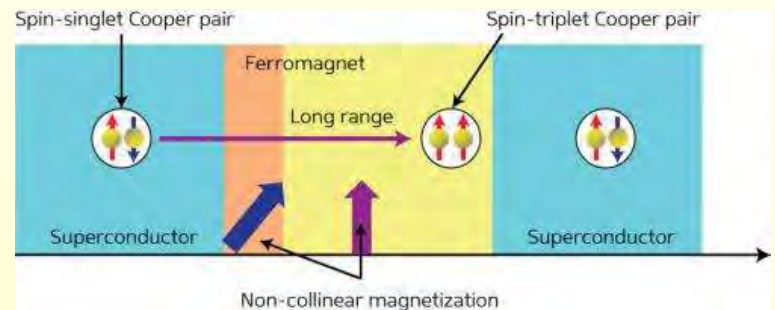


A. Singh, S. Voltan, K. Lahabi, and J. Aarts, "Colossal Proximity Effect in a Superconducting Triplet Spin Valve Based on the Half-Metallic Ferromagnet CrO_2 ," Phys. Rev. X **5**, 021019 (2015).

Hikino, S. & Yunoki, S.

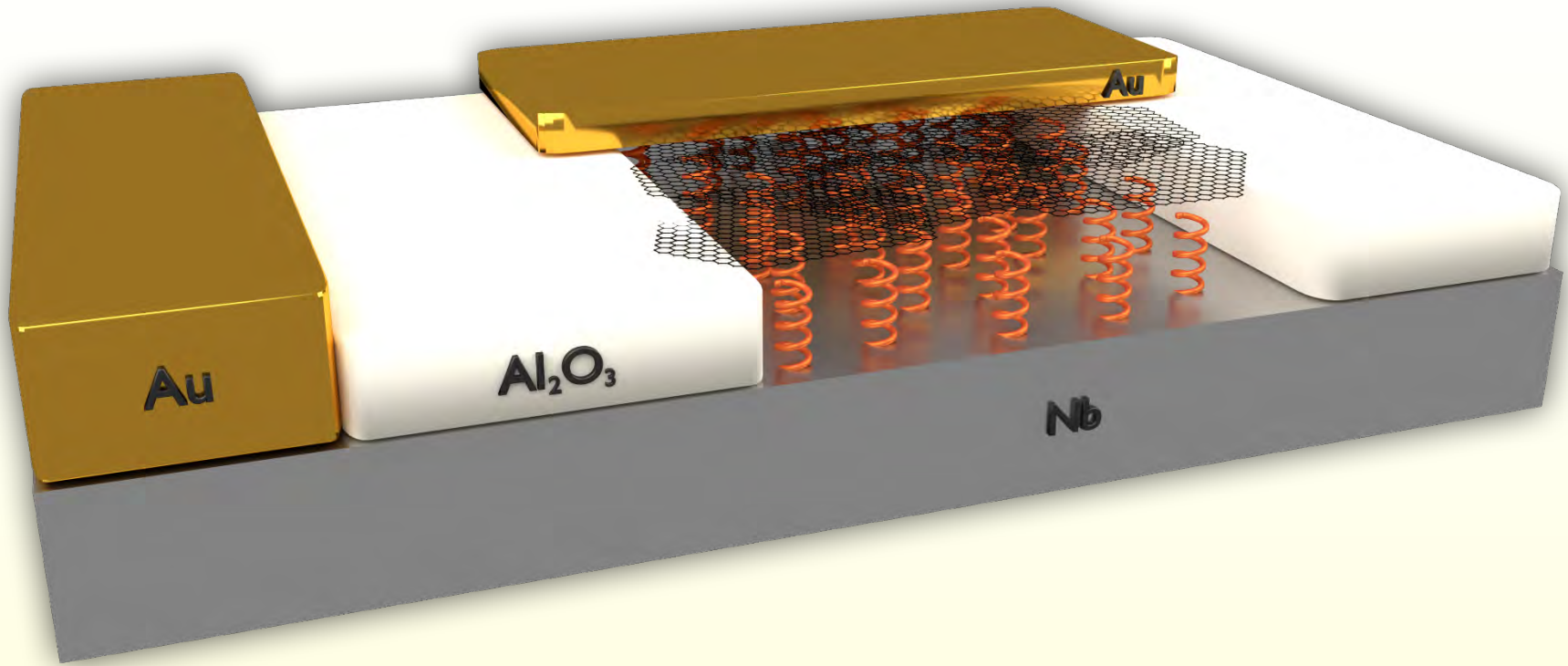
Long-range spin current driven by superconducting phase difference in a Josephson junction with double layer ferromagnets,

Physical Review Letters **110**, 237003 (2013).



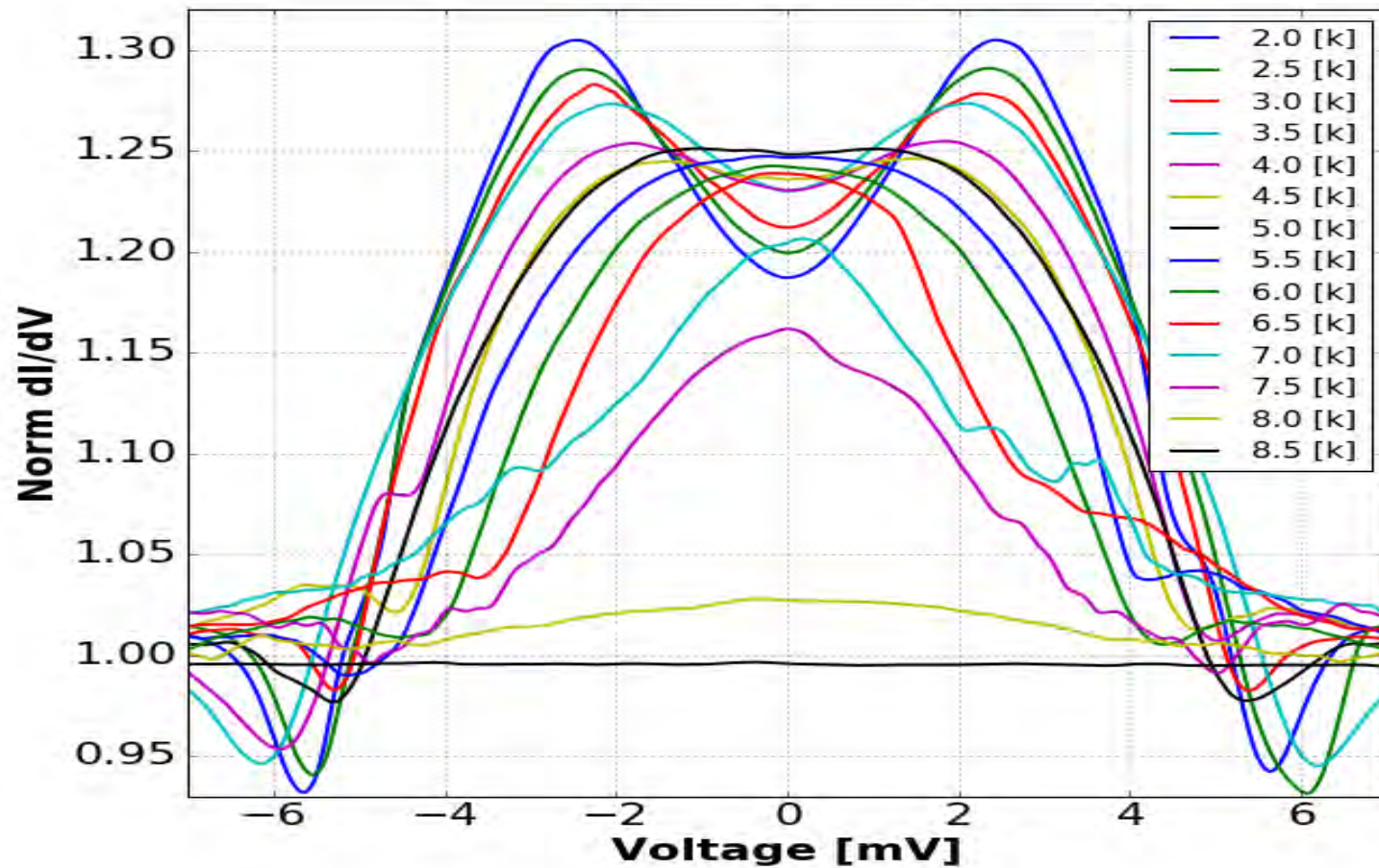
Q N E
L a b

Device Sketch

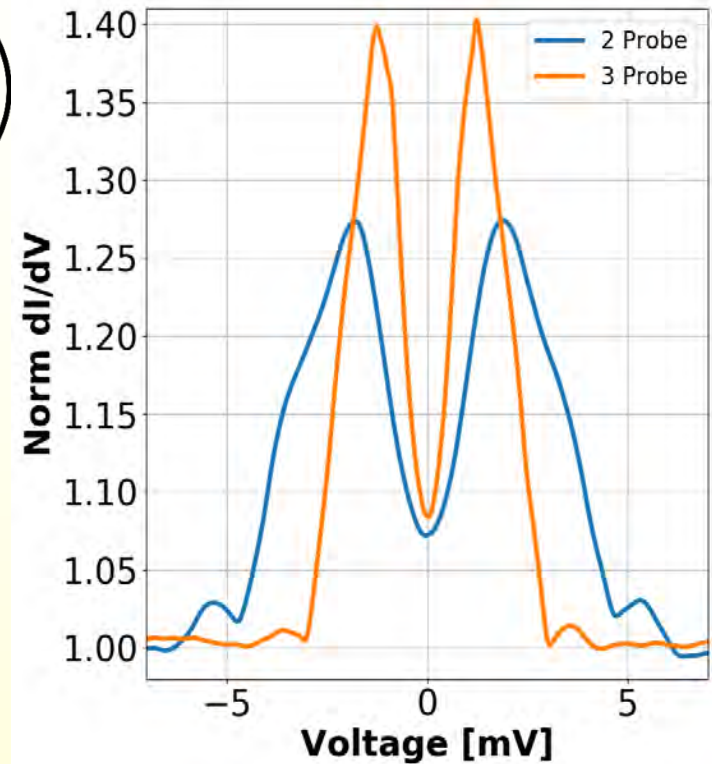
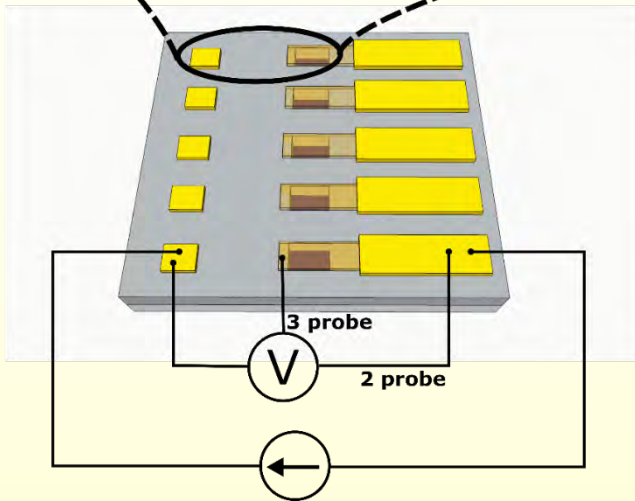
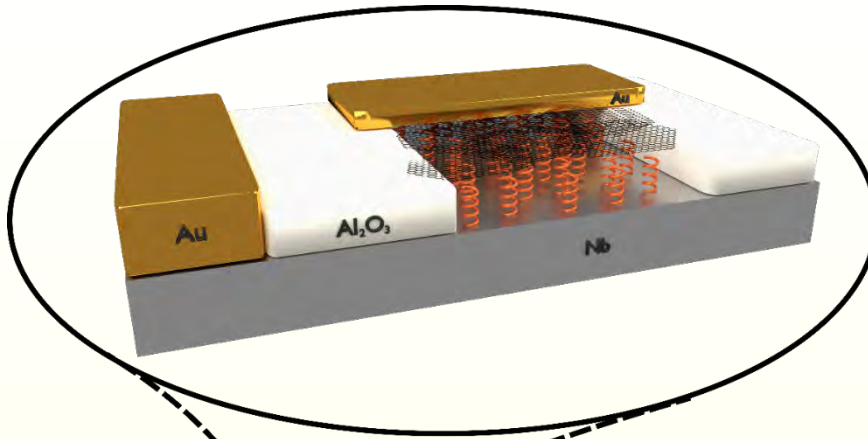


the junction measured consists of a Nb substrate, chiral polyaniline molecules, conductive graphene flakes and a top gold electrode. The measurement is done between the gold electrodes

Junction dI/dV Vs. V

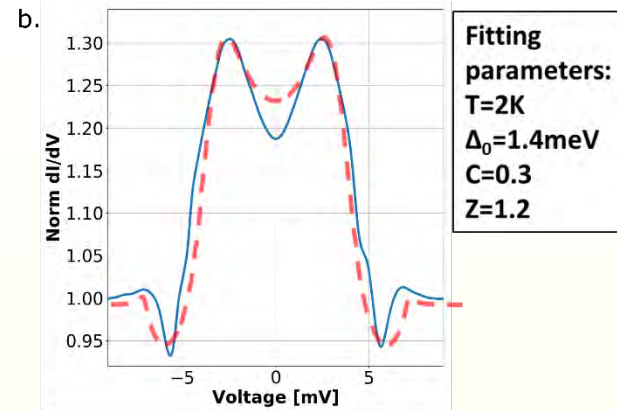
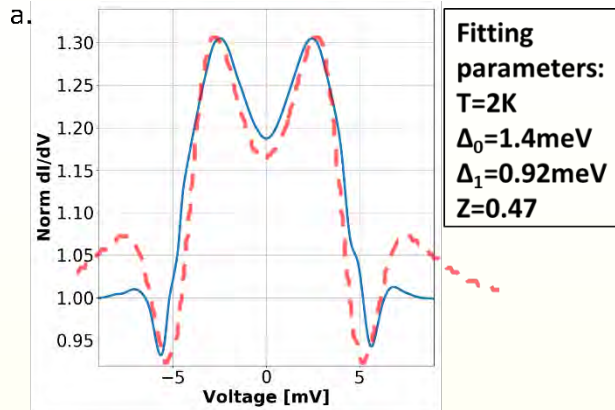


3 probe configuration

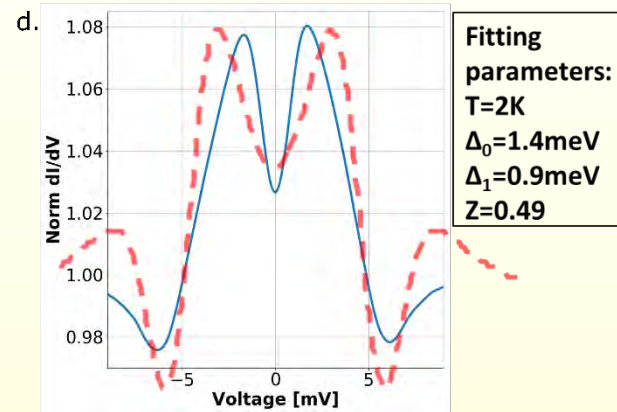
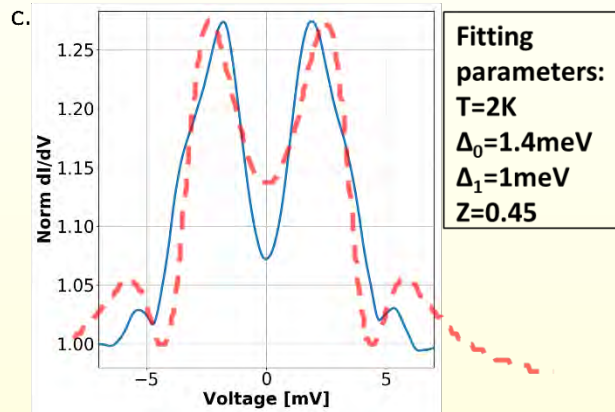


Theoretical fits

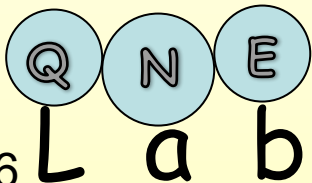
Low Z
Two gap
model



High Z
P wave
model

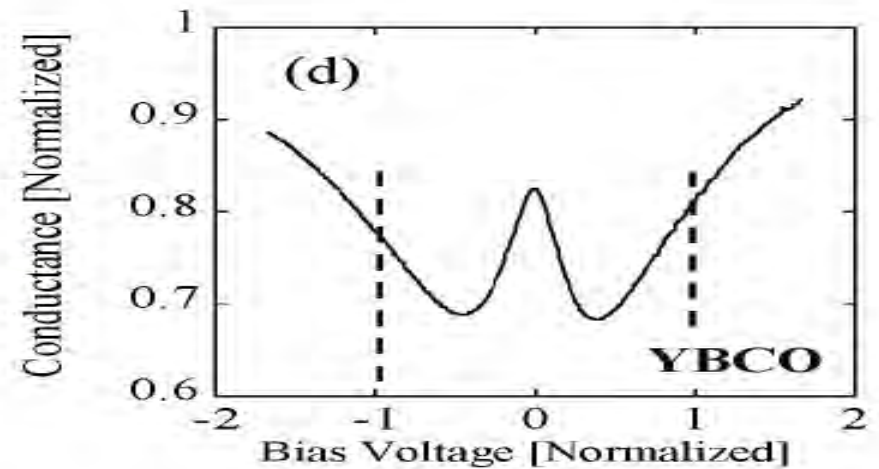
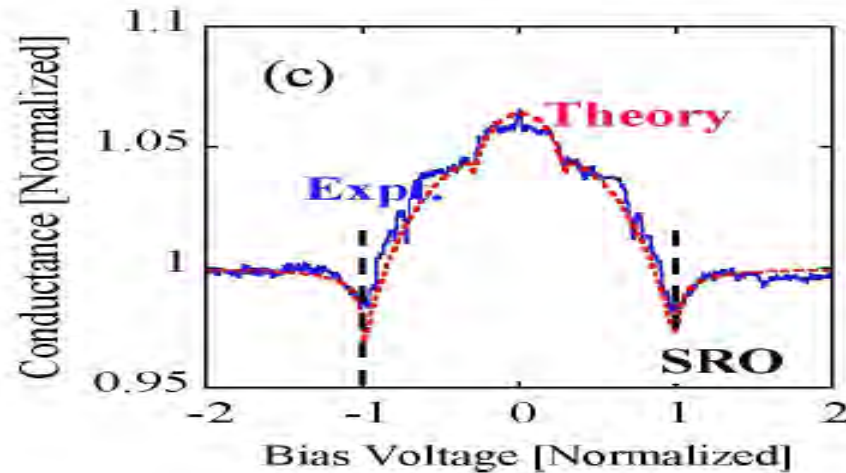
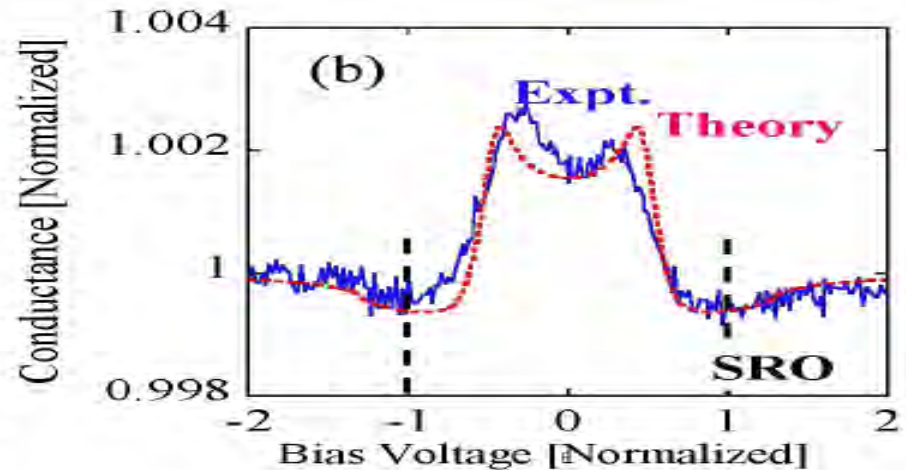
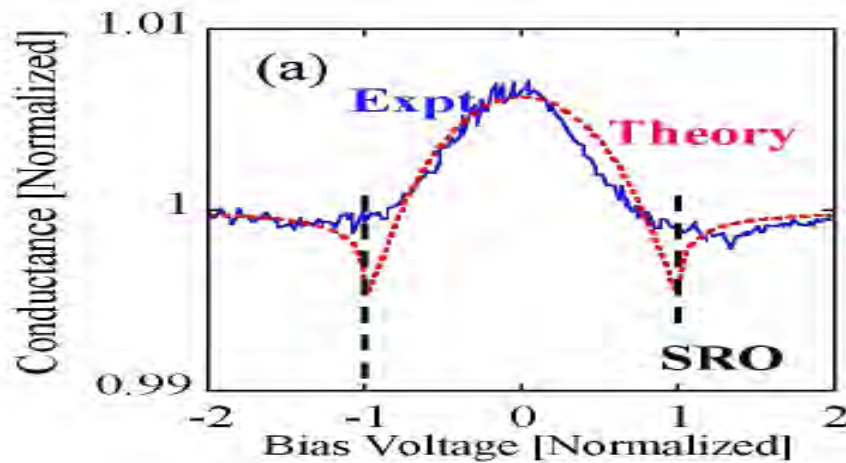


Anisotropy factor, C, is introduced, and in the equation above Δ_0 is replaced by $\Delta_0 = \Delta_0(1 + C * \cos(4\theta))$.



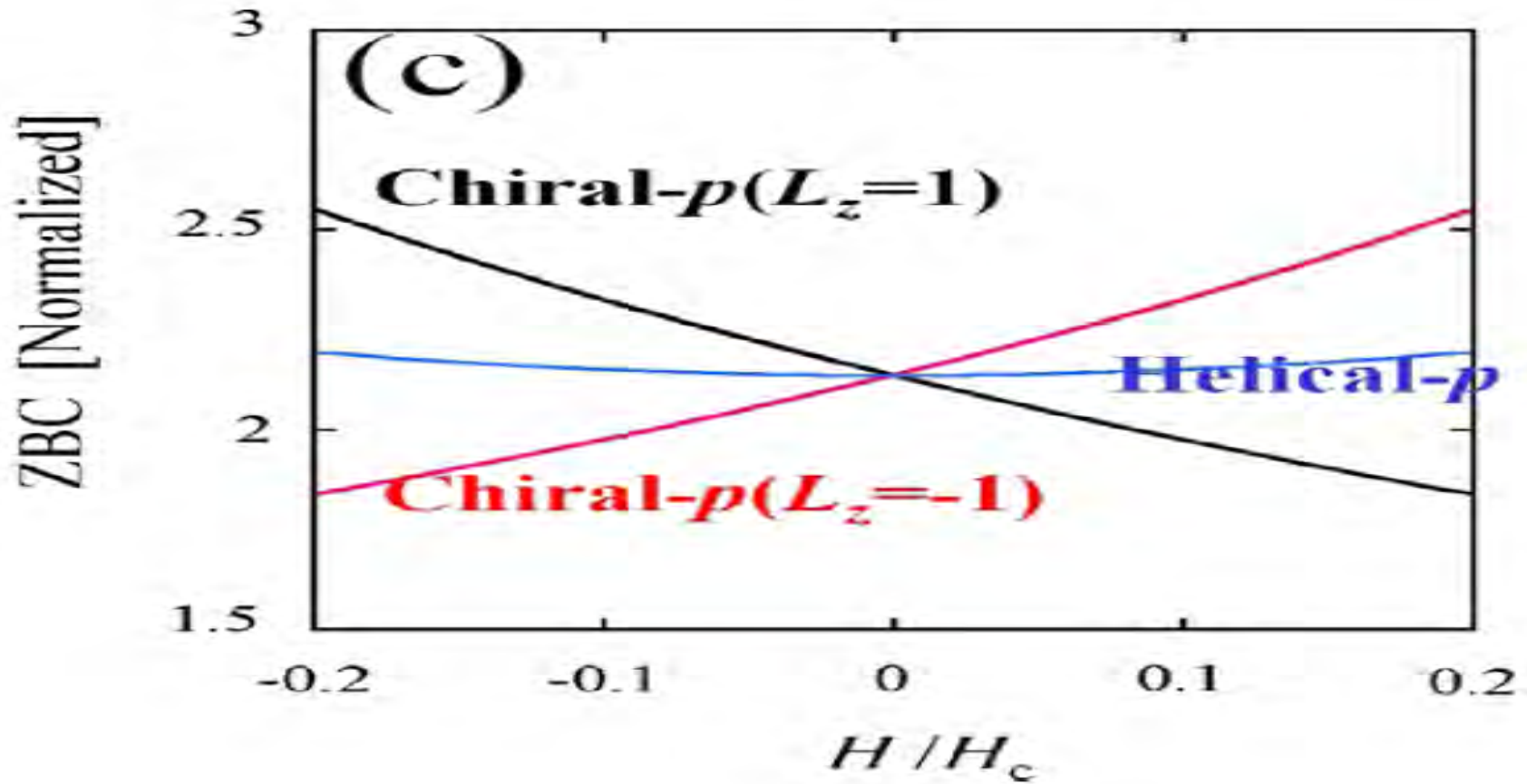
Results- analysis

Similar results were measured experimentally on P-wave superconductor Sr_2RuO_4



S. Kashiway *et al.*, "Edge States of Sr_2RuO_4 Detected by In-Plane Tunneling Spectroscopy," *Phys. Rev. Lett.*, vol. 107, no. 7, p. 077003, Aug. 2011.

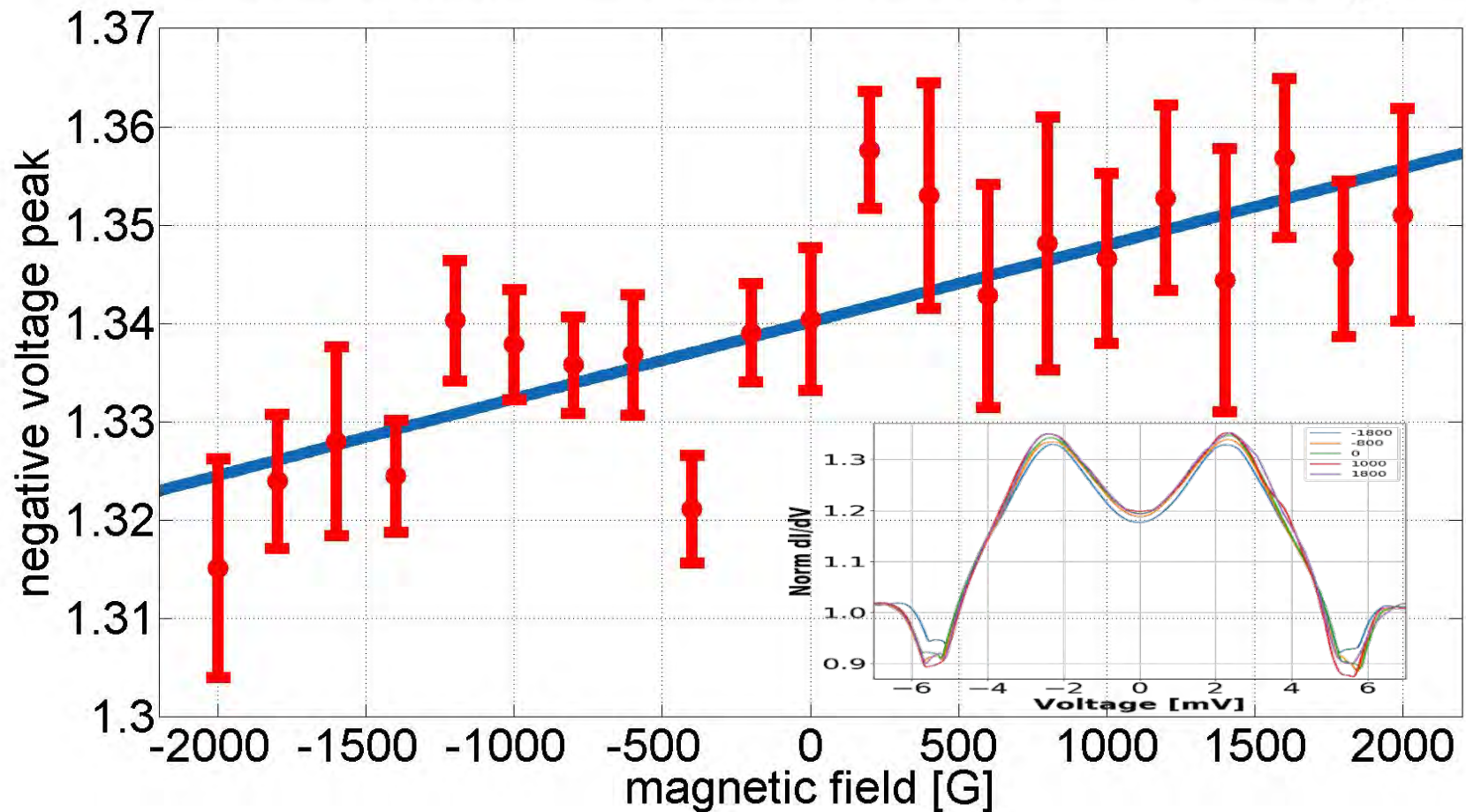
Chiral P ZBC



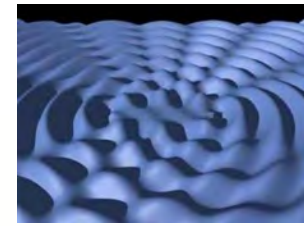
S. Kashiwaya, H. Kashiwaya, K. Saitoh, Y. Mawatari, and Y. Tanaka, "Tunneling spectroscopy of topological superconductors," *Phys. E Low-Dimens. Syst. Nanostructures*, vol. 55, pp. 25–29, Jan. 2014.

Magnetic measurements at 1.7K may hint to induced long range order

peak intensity as a function of magnetic field bellow H_{c1}

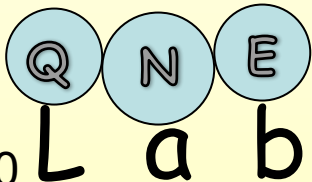
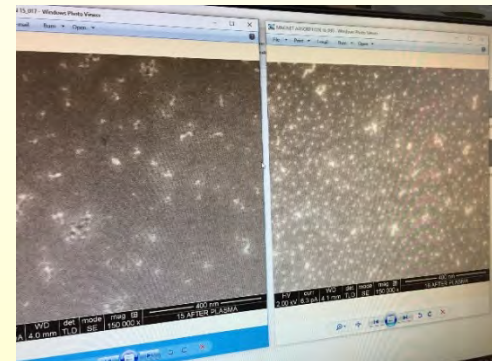


Collective effects



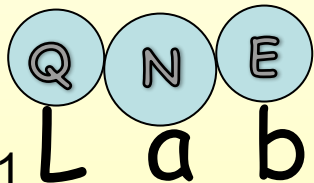
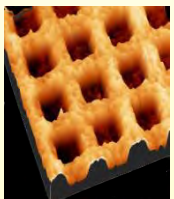
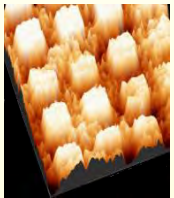
- We see a strong surface spin interface effect using chiral molecules in equilibrium.
- We may see collective long range coherent ordering
- Or local magnetization and Zeeman splitting in the molecules
- Simple superconducting spintronics devices can be realized.

Can we see the opposite effect?
Magnetization of the surface
influence the adsorption rate by CISS?



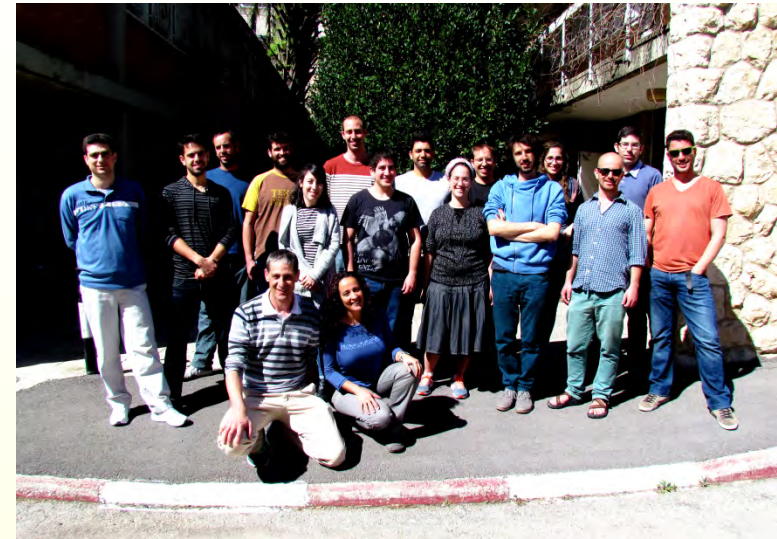
Summery We show a simple way to solve material and current problems

- CISS based devices work as optical/electrical memory at ambient in a device of 40x40 nm.
- It works as a reading head at ambient with dimensions of 10x10 nm.
- The hysteresis is “meristor like” which can be used as embedded memory in integrated circuits.
- Induced local magnetization switching by local adsorption of chiral molecules on ferromagnets
- No need for current or external magnetic field – down to single domain size only 0.5nm deep.





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